

FIG.1A

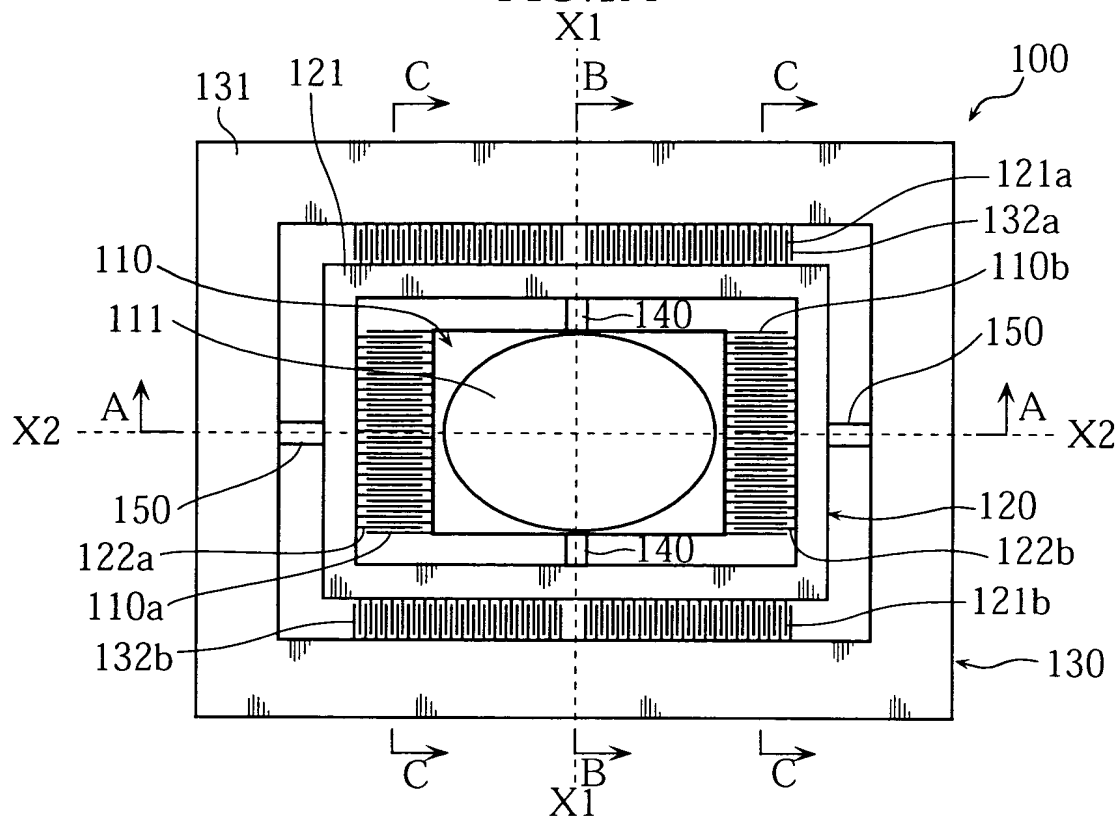
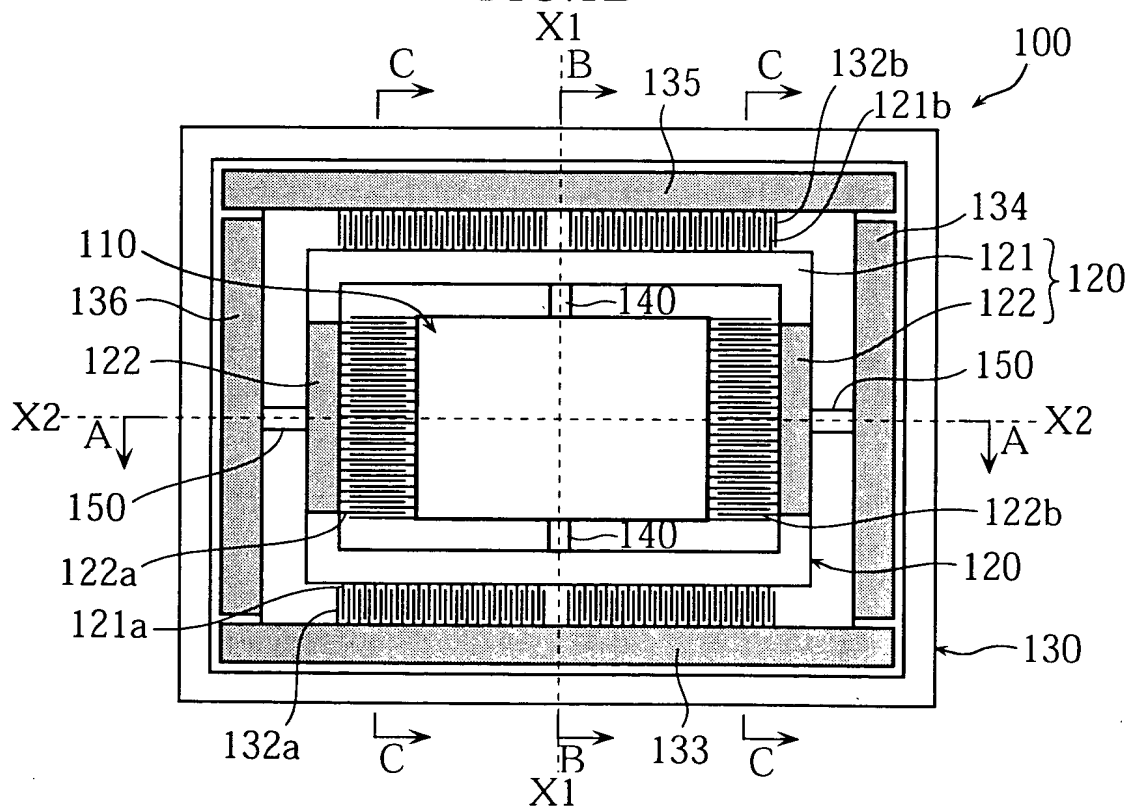


FIG.1B





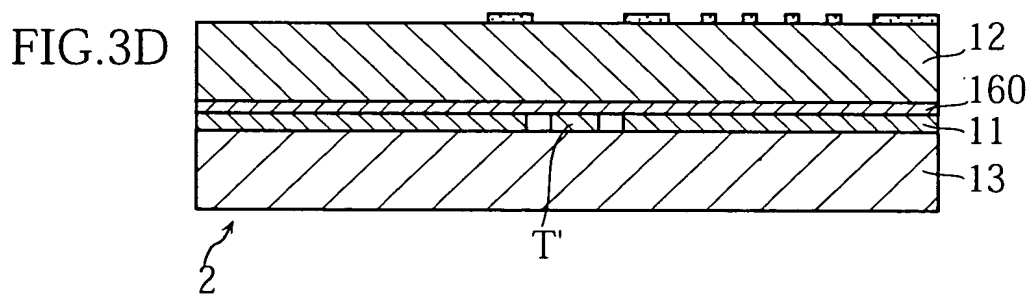
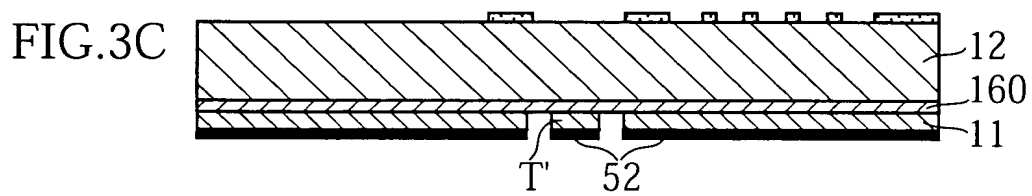
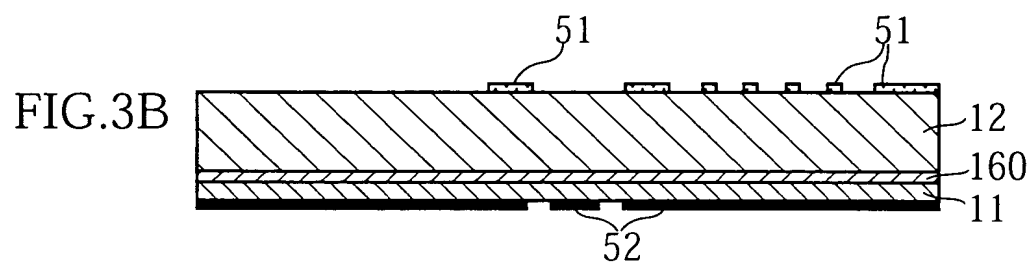
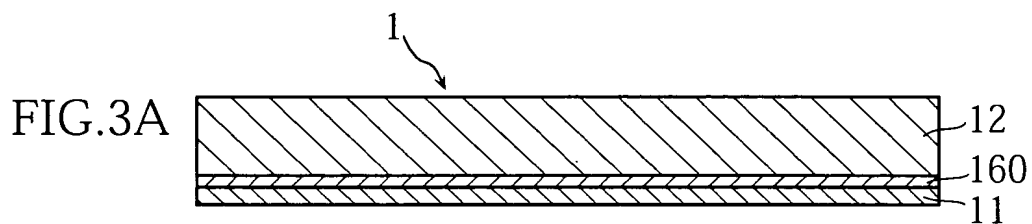


FIG.4A

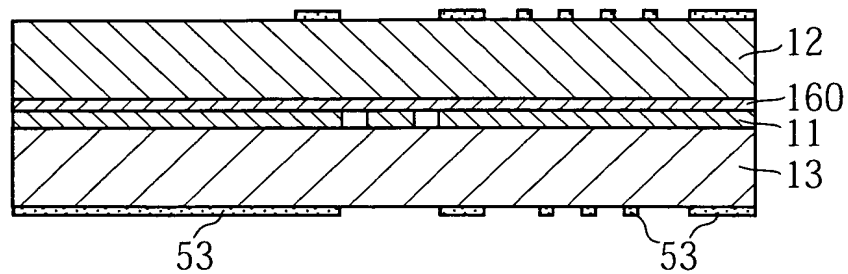


FIG.4B

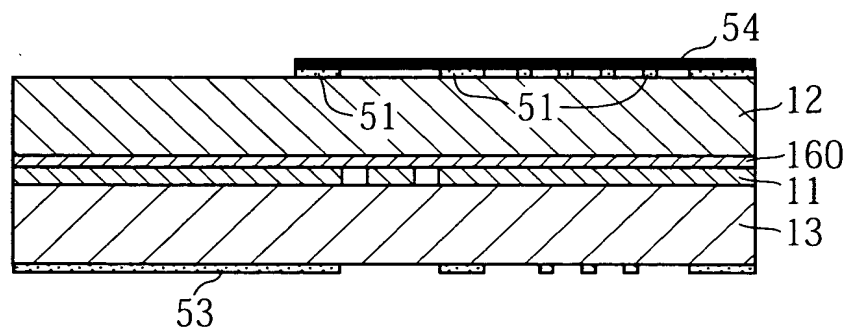


FIG.4C

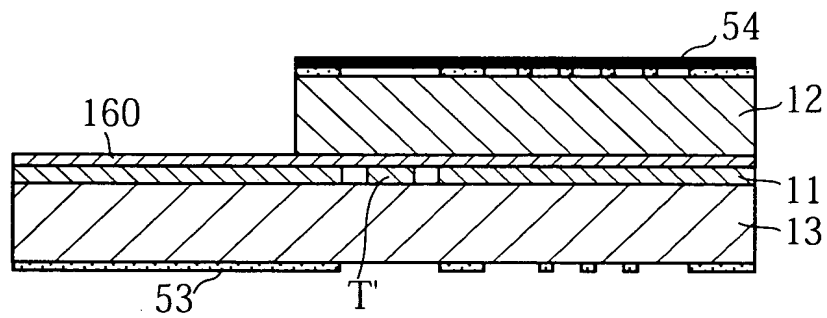


FIG.4D

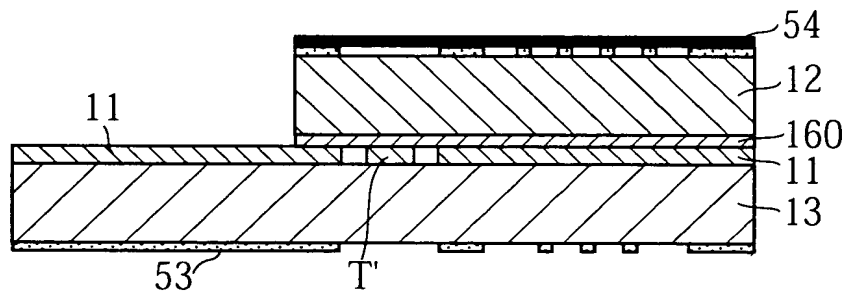


FIG.4E

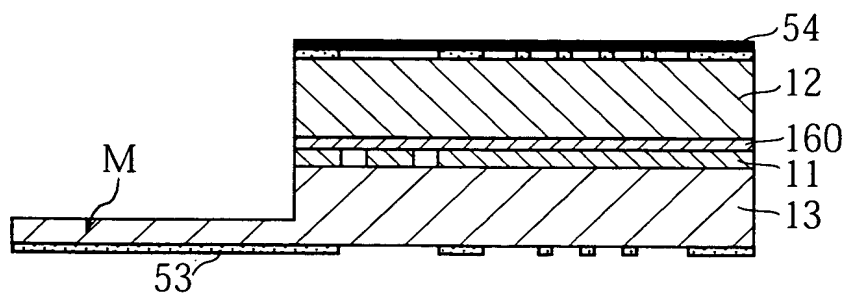


FIG.5A

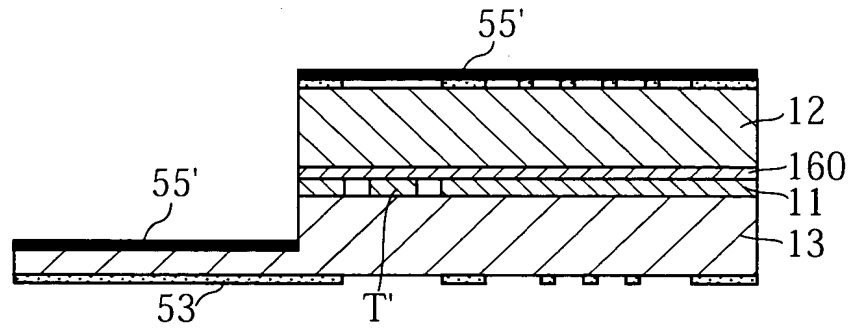


FIG.5B

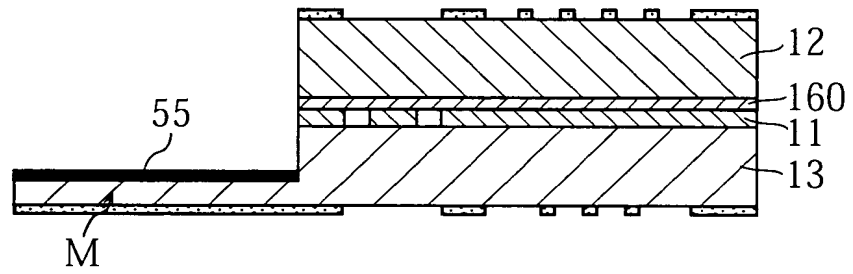


FIG.5C

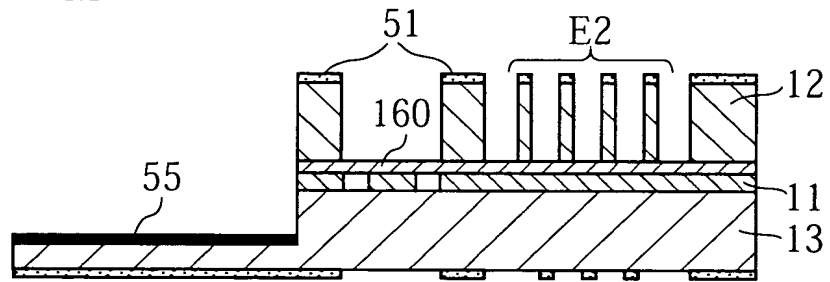


FIG.5D

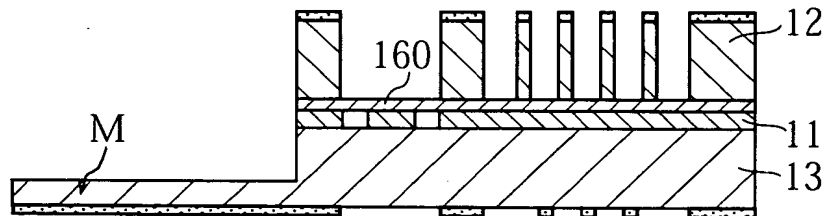


FIG.6A

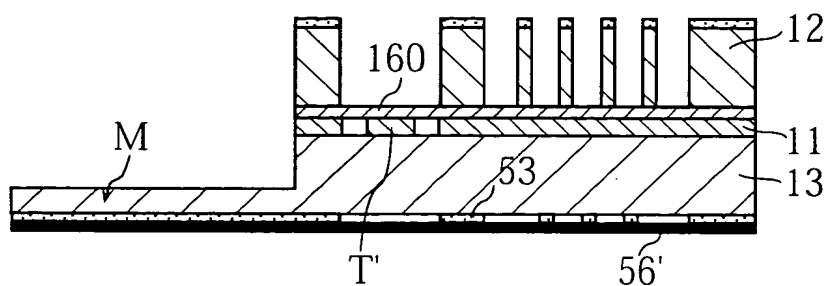


FIG.6B

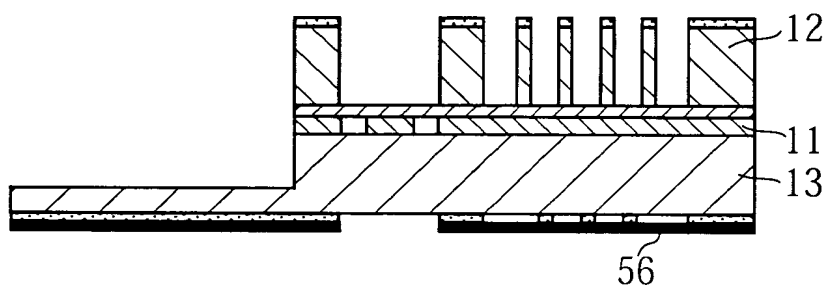


FIG.6C

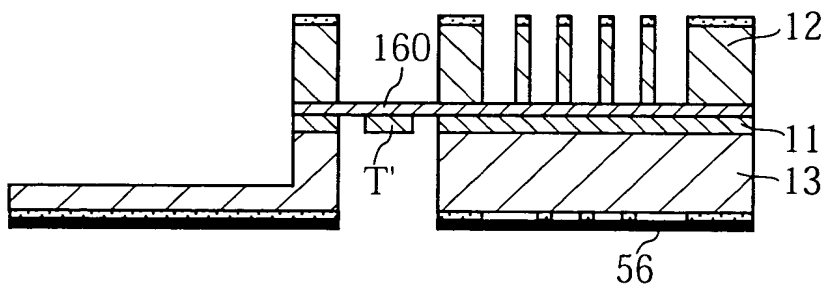
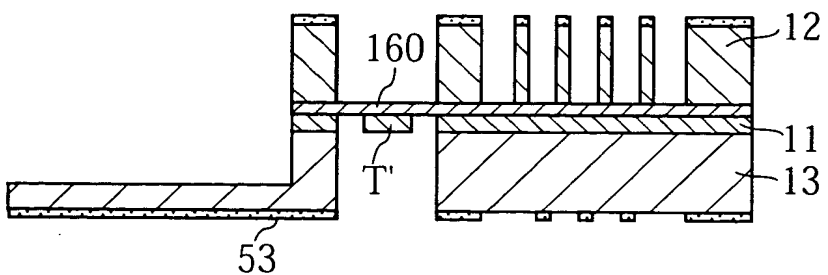
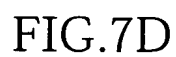
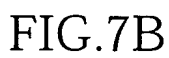
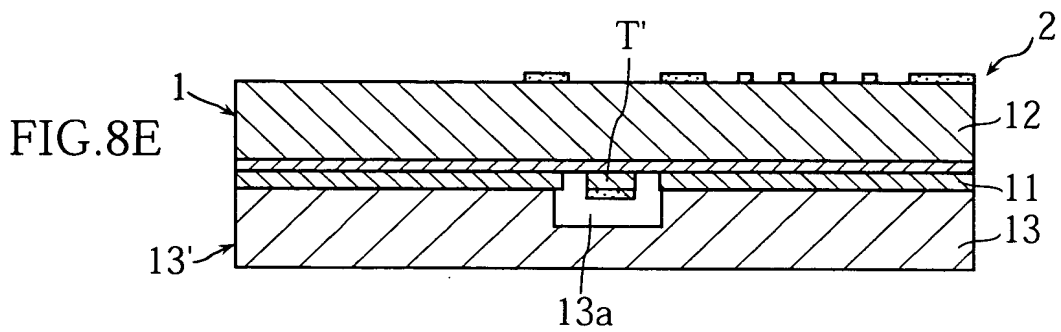
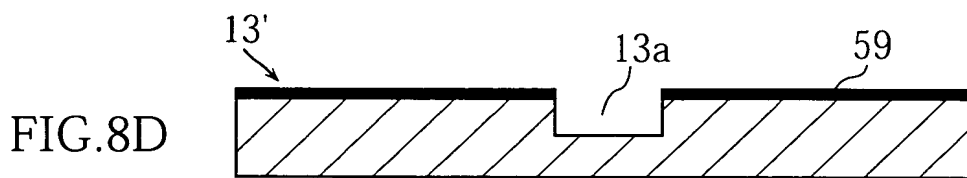
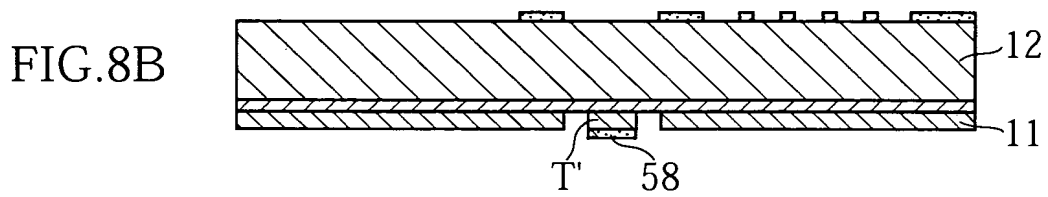
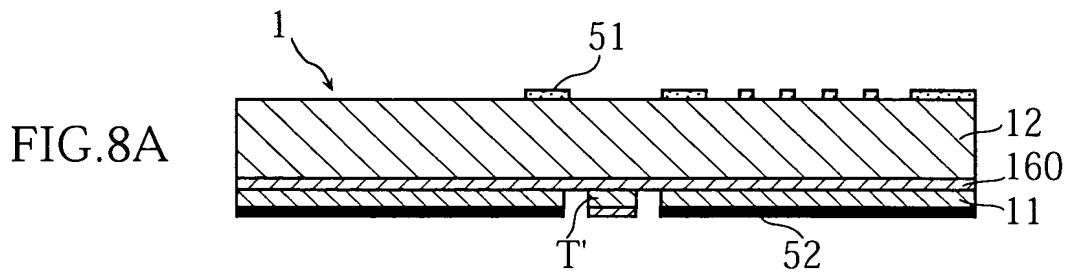


FIG.6D

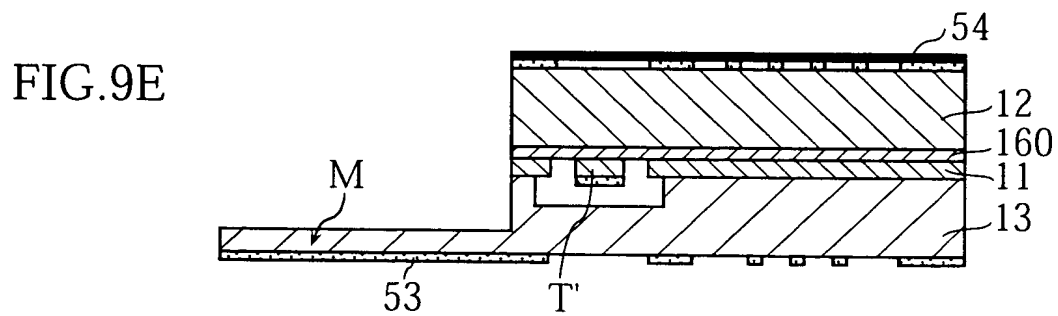
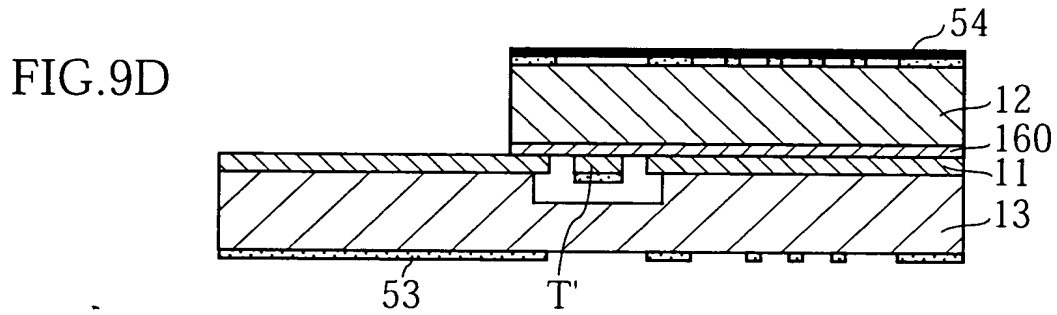
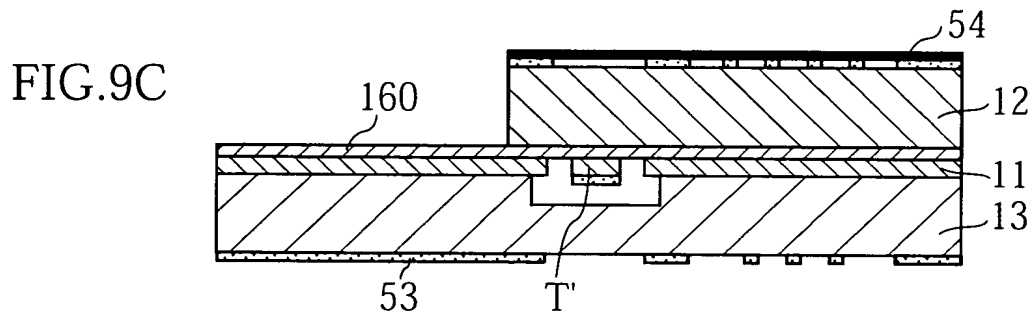
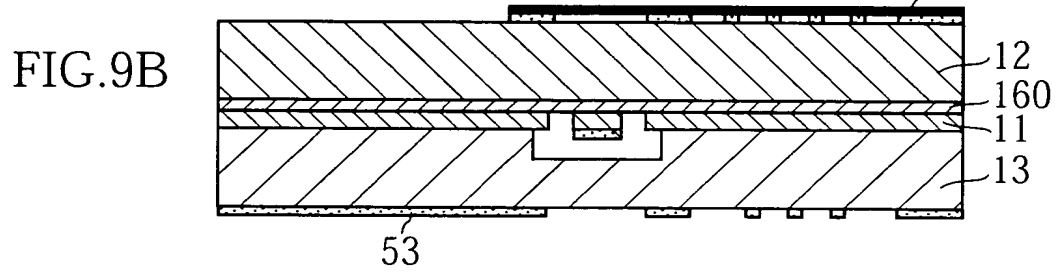
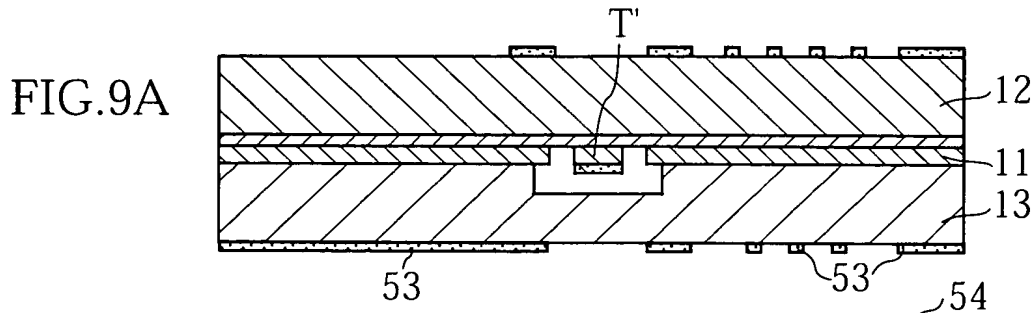


**SECRET**









[illegible]

Fig. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 13, a gate layer 11, a gate electrode 12, a gate insulating layer 160, and a metal layer M.

FIG.11A

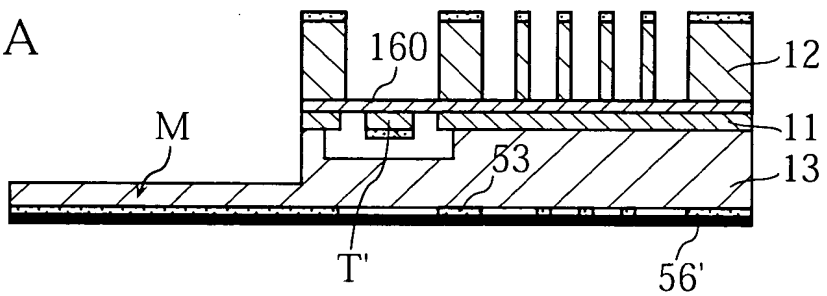


FIG.11B

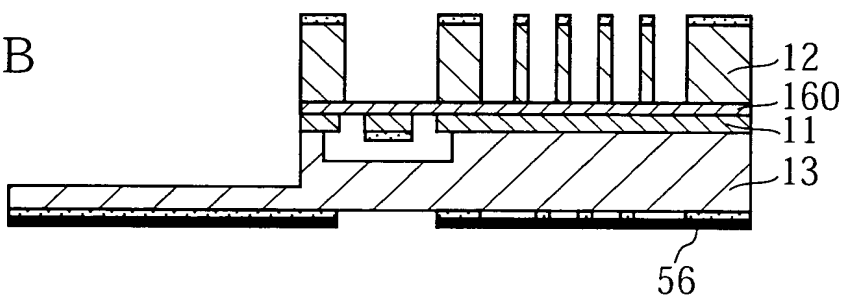


FIG.11C

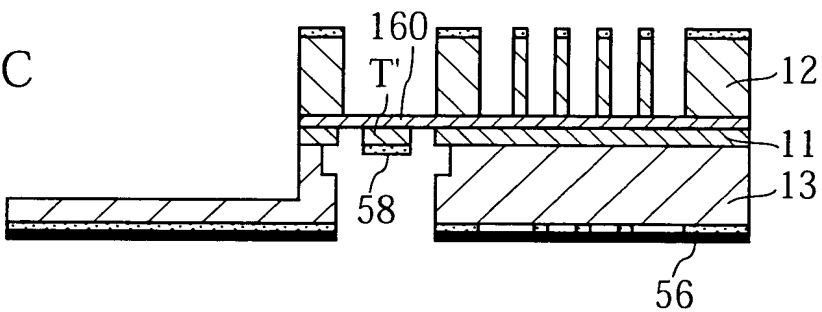


FIG.11D

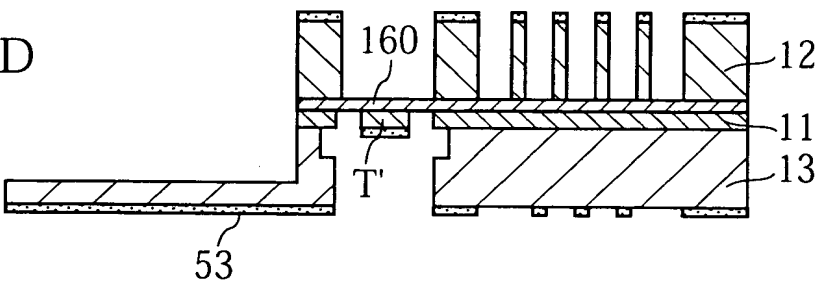


FIG.12A

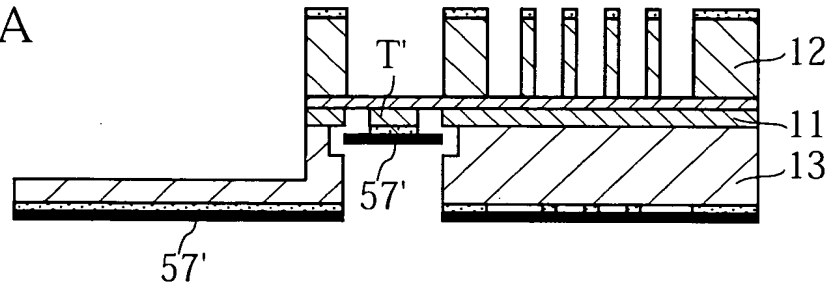


FIG.12B

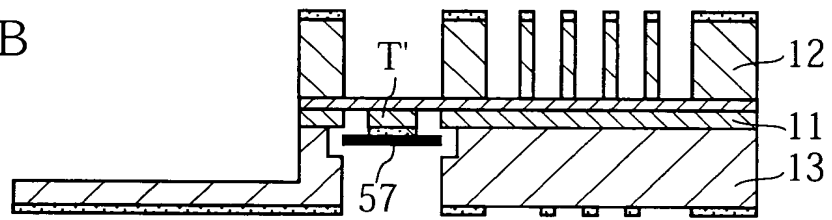


FIG.12C

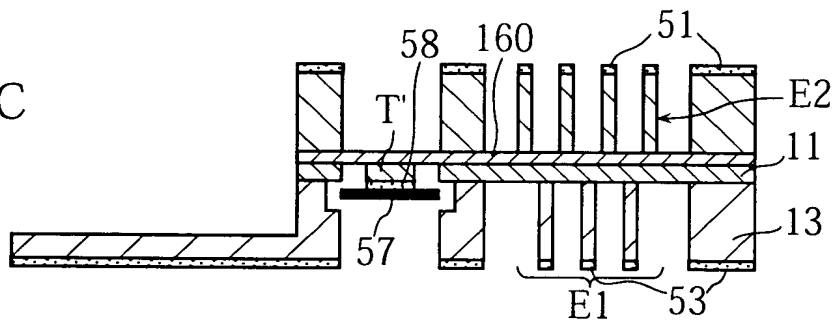
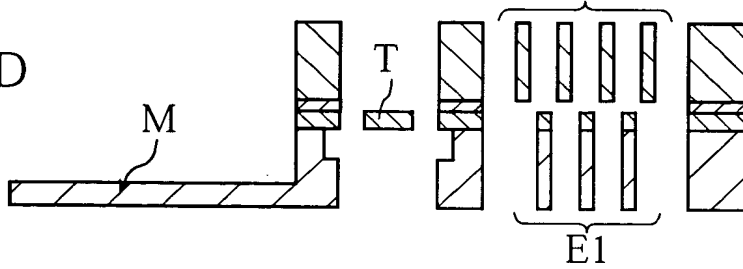


FIG.12D



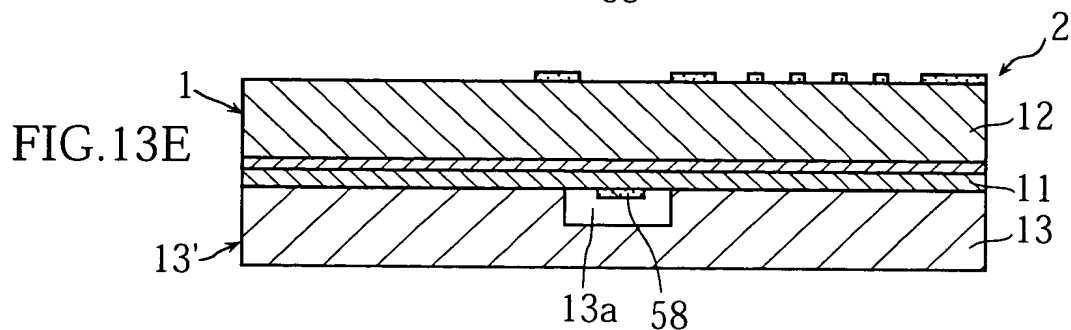
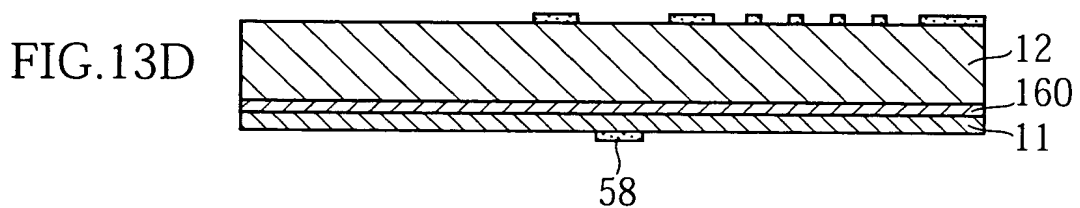
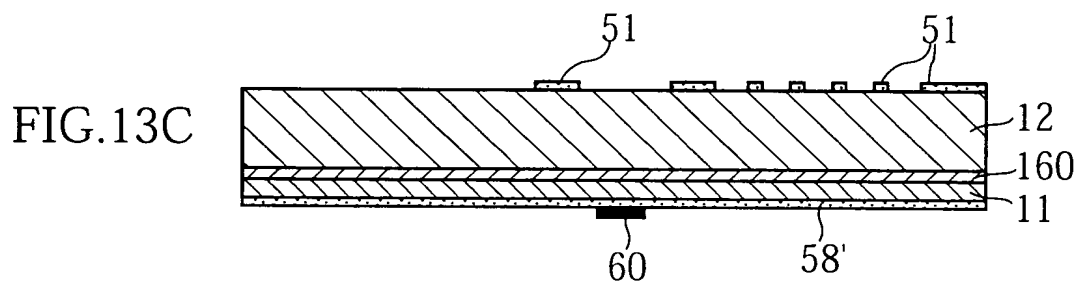
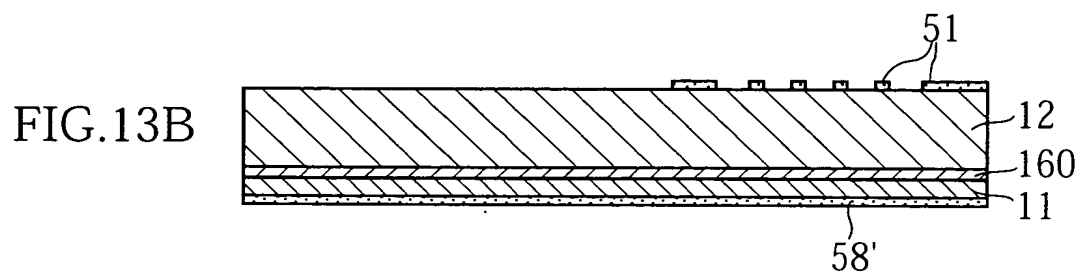
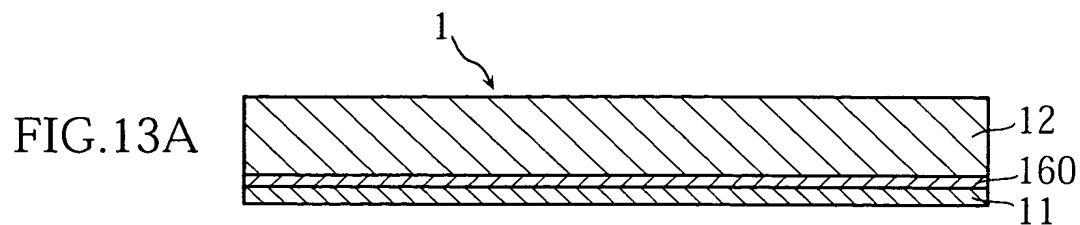


FIG.14A

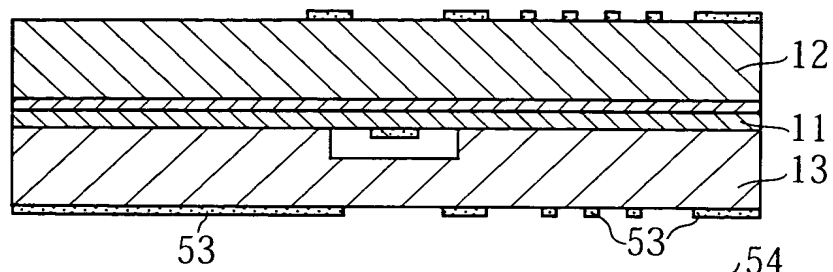


FIG.14B

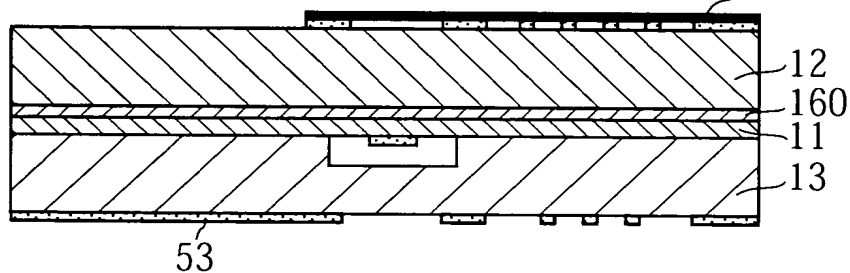


FIG.14C

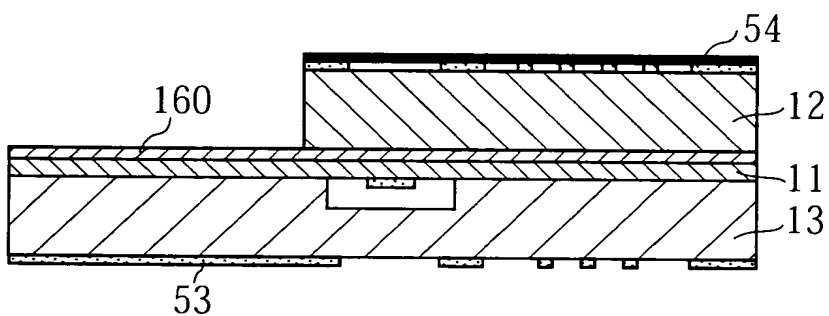


FIG.14D

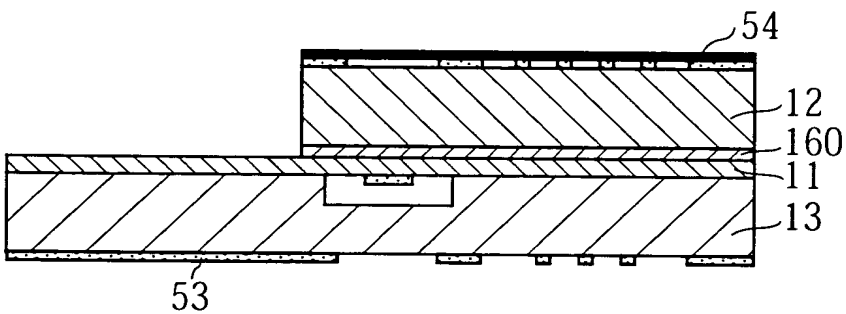
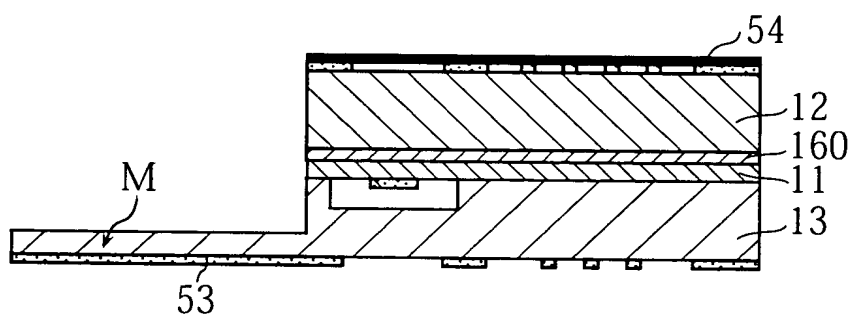
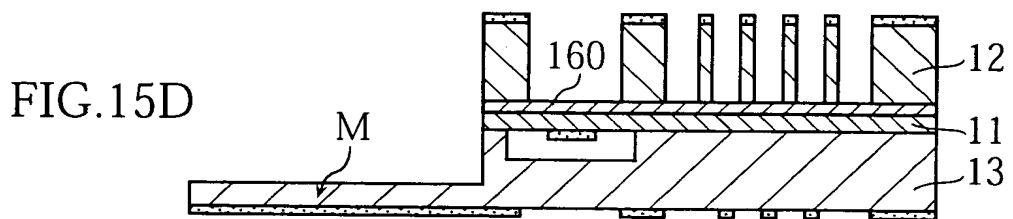
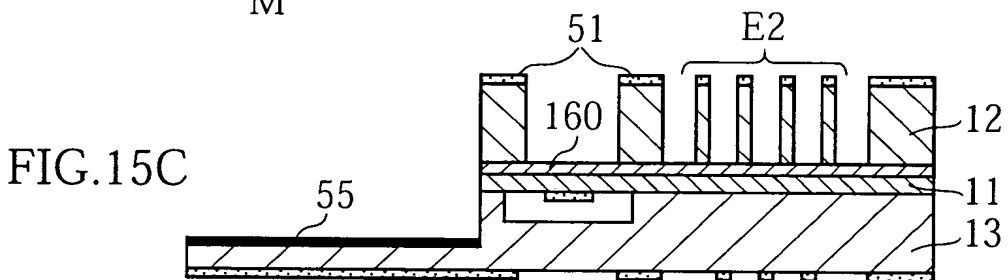
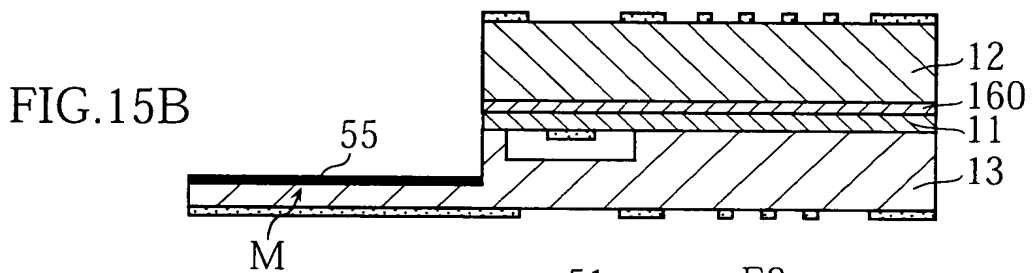
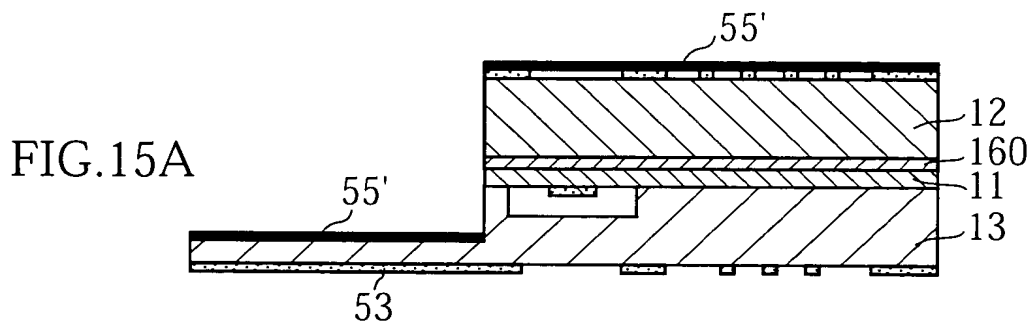


FIG.14E





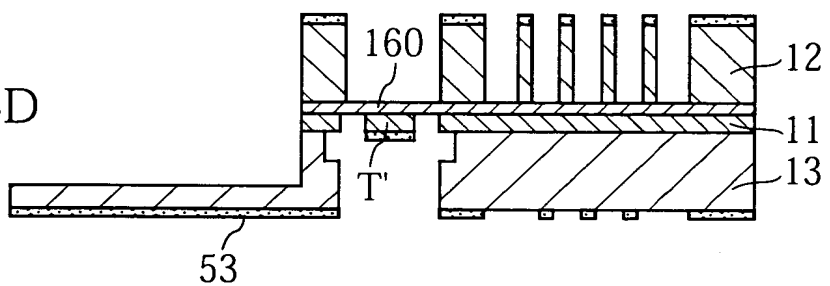
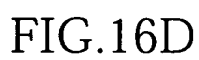
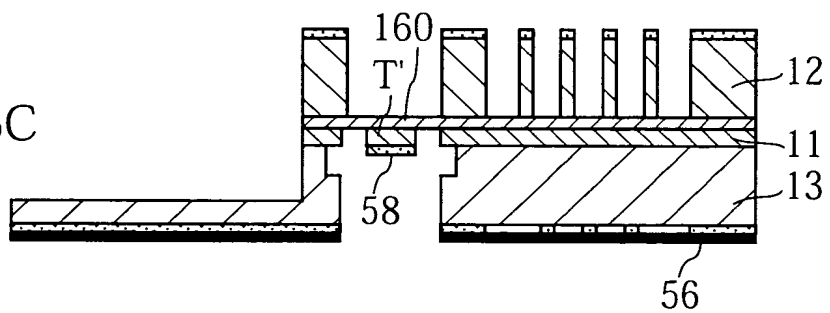
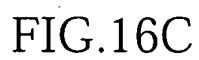
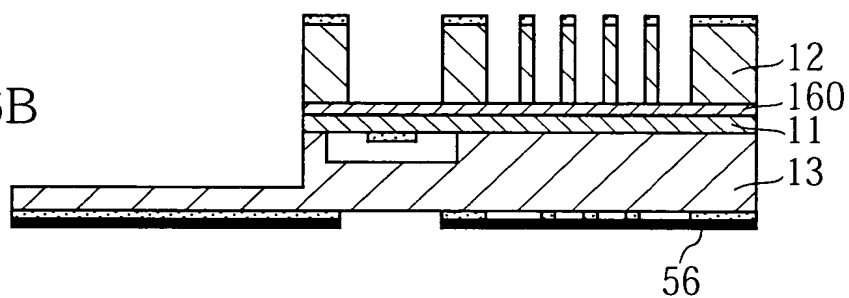
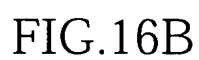
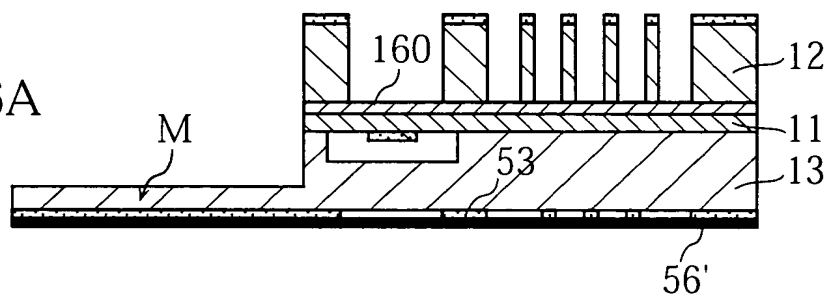
[illegible]



FIG.17A

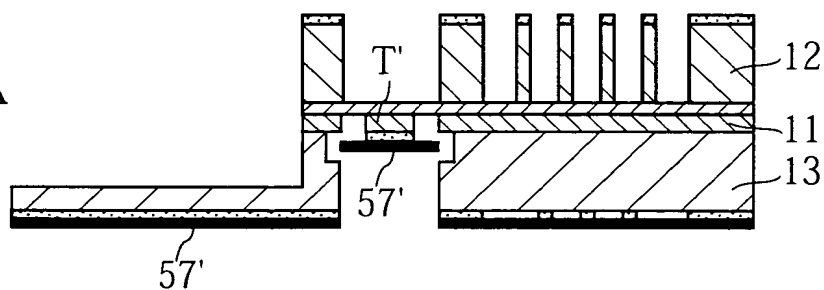


FIG.17B

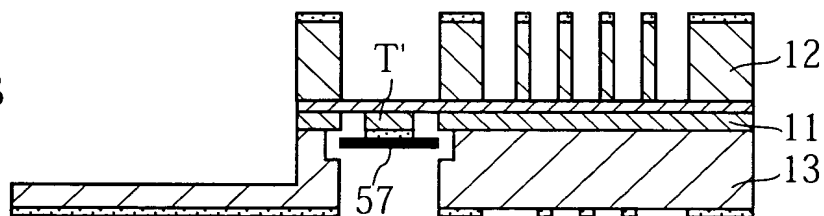


FIG.17C

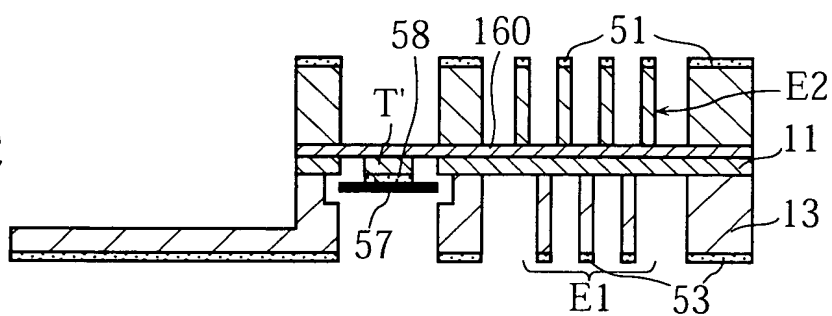
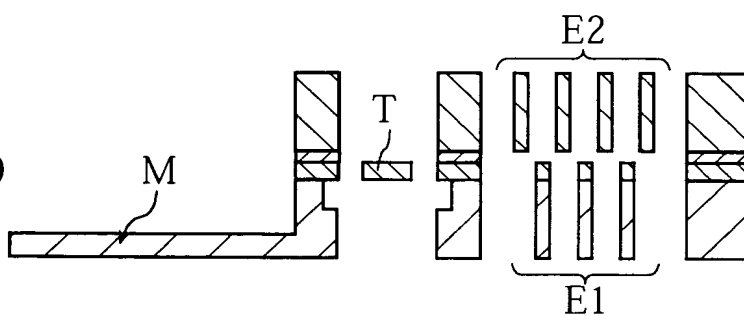
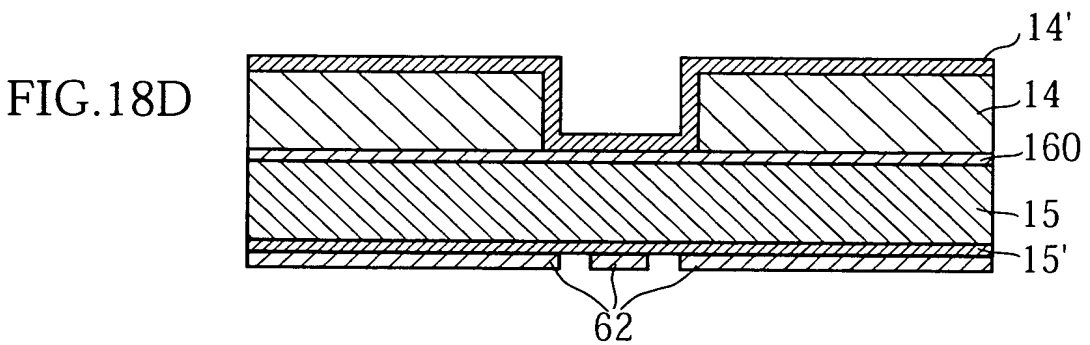
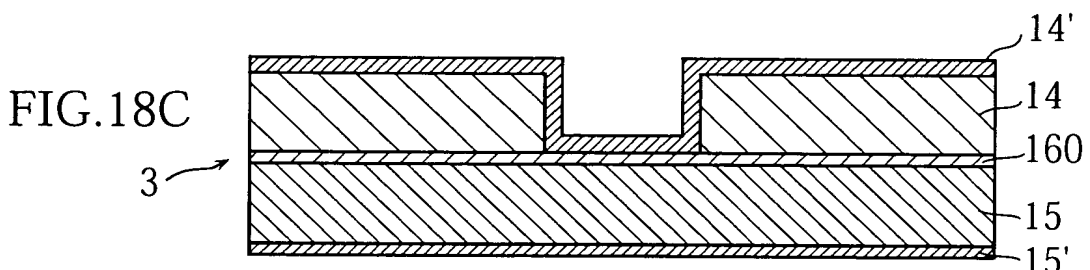
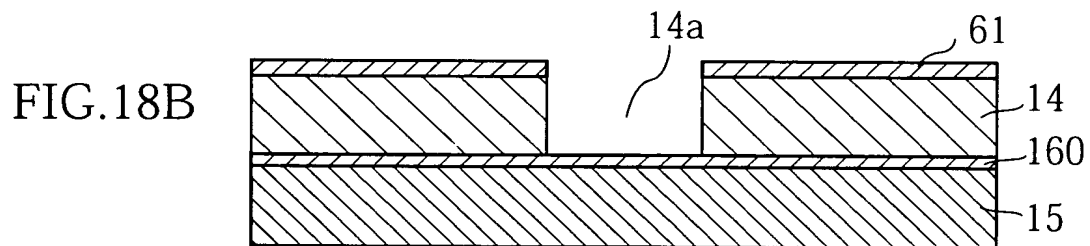
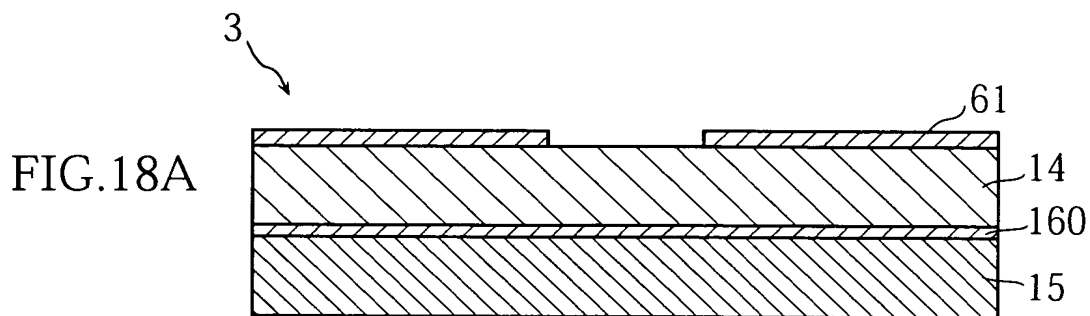
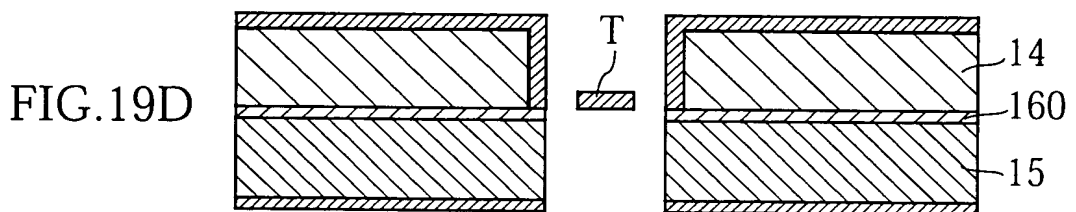
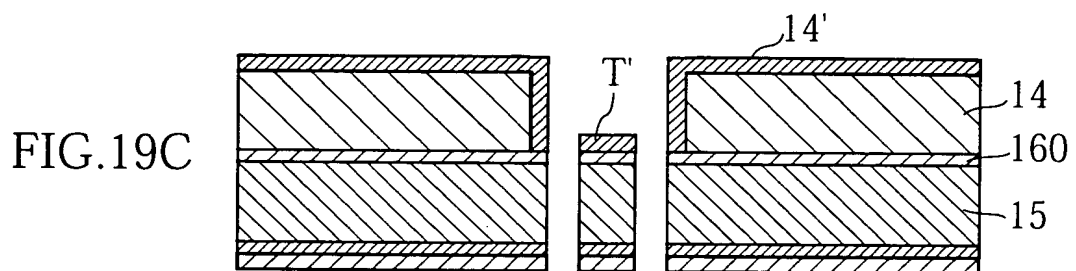
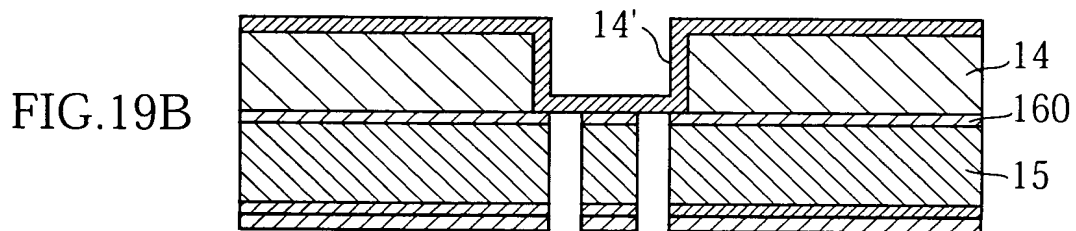
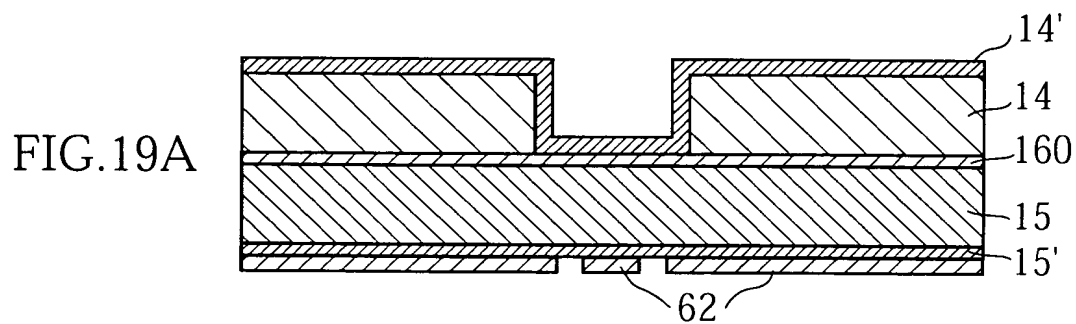
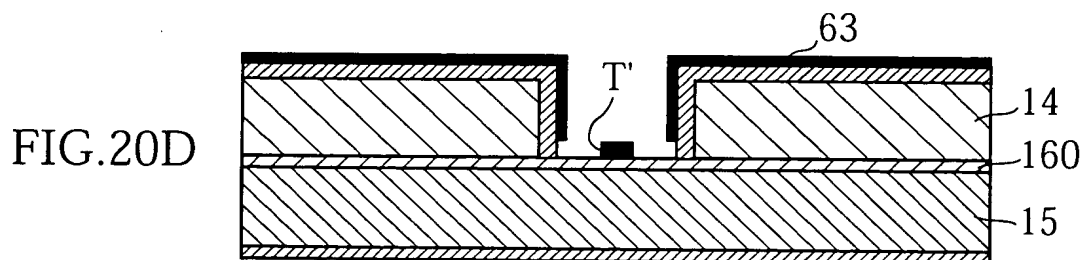
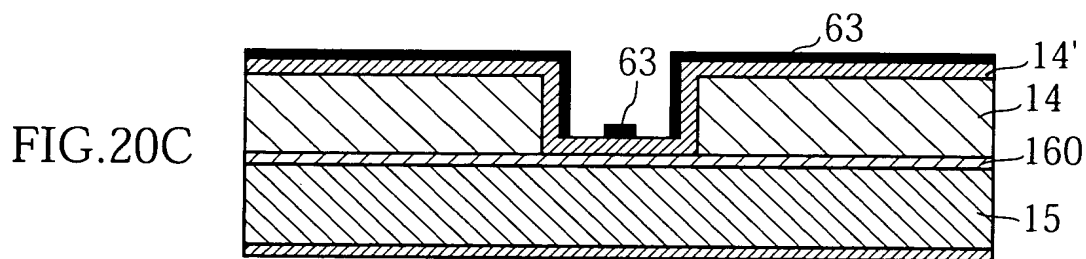
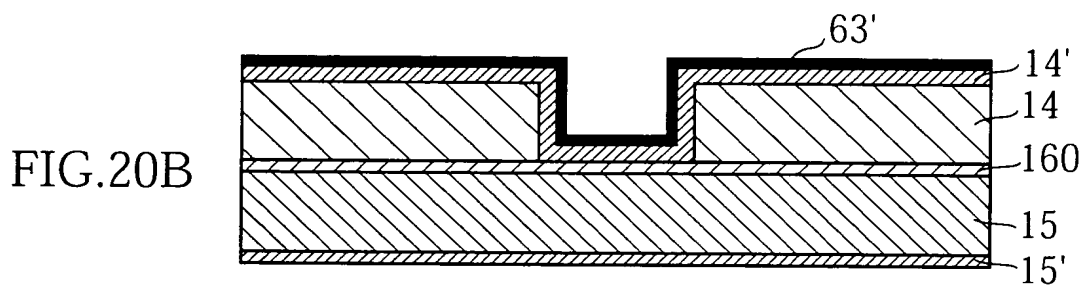
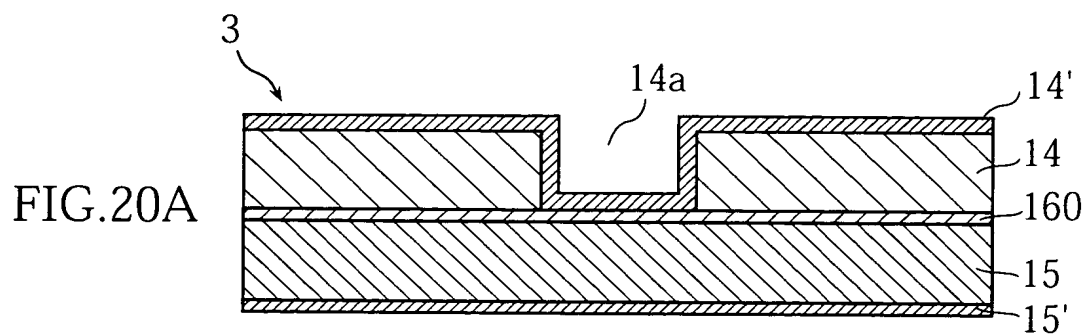


FIG.17D









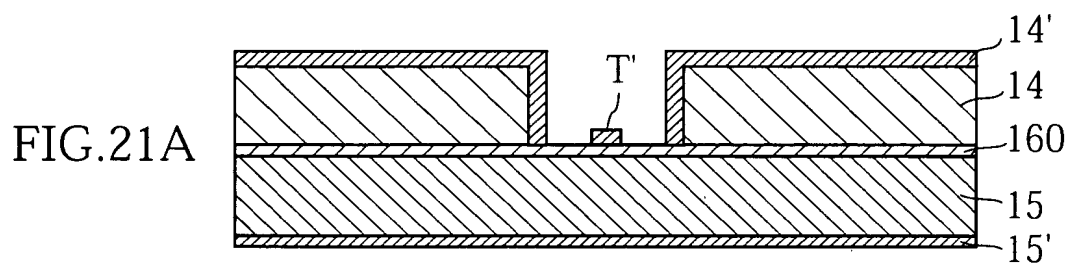


FIG. 21B

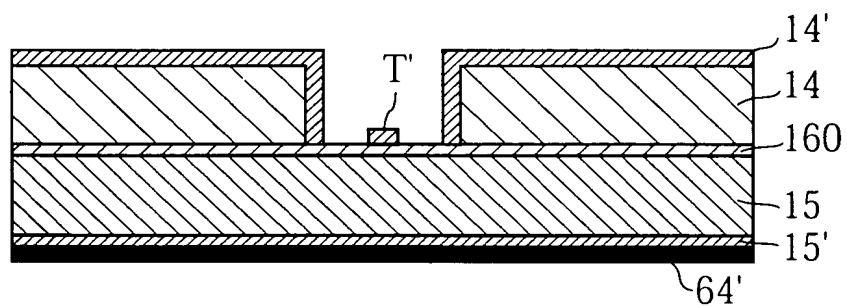


FIG. 21C

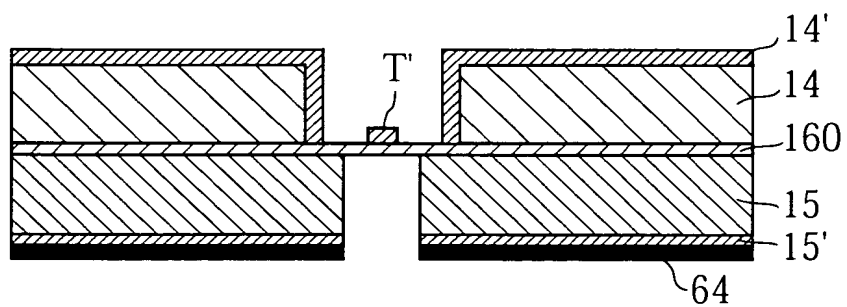
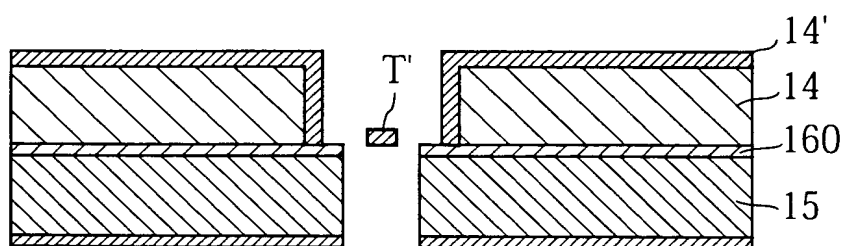


FIG. 21D



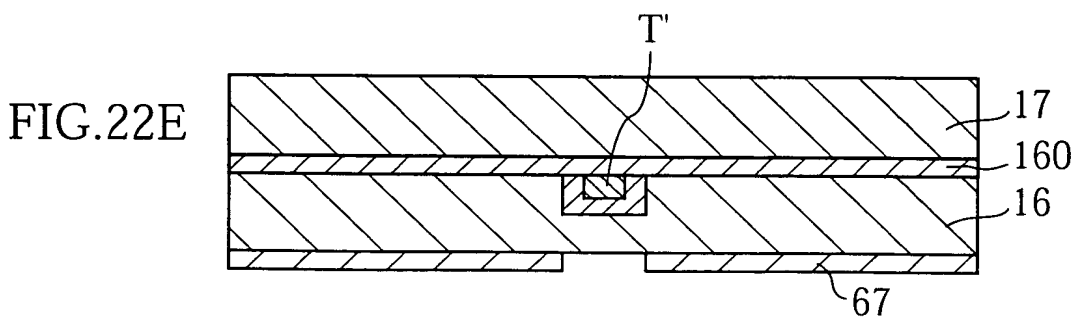
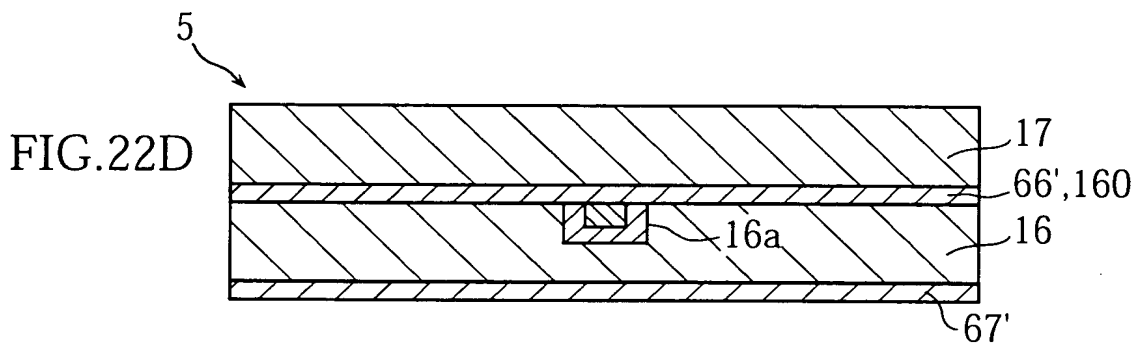
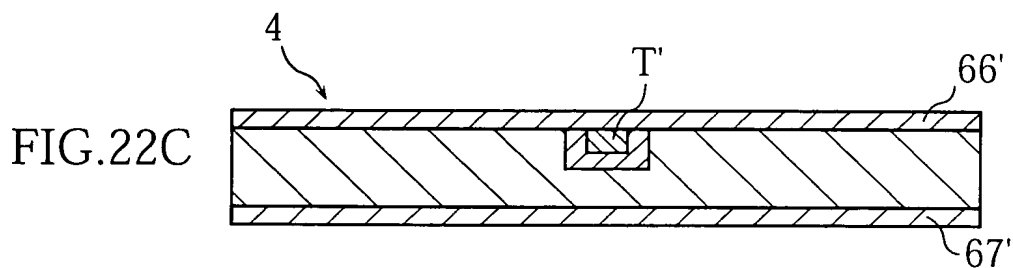
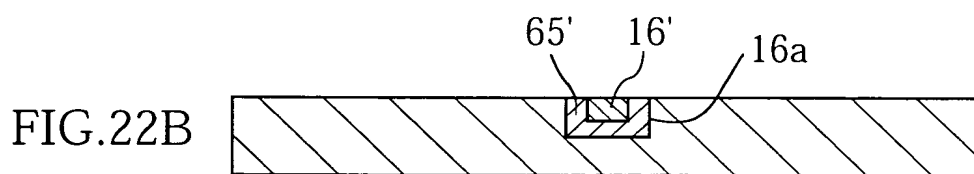
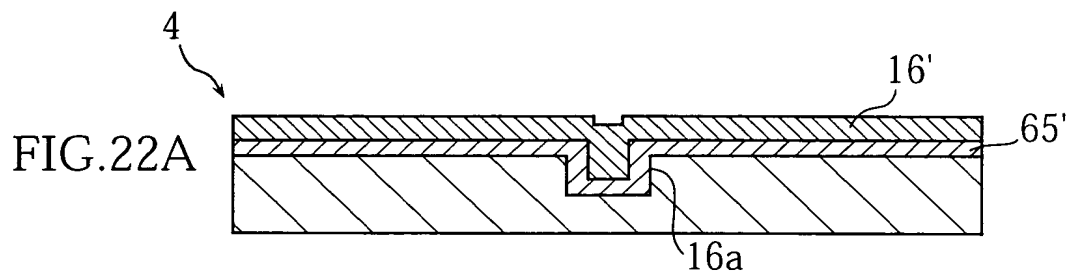


FIG.23A

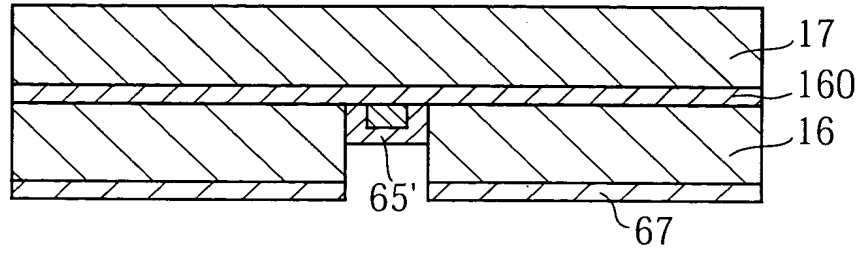


FIG.23B

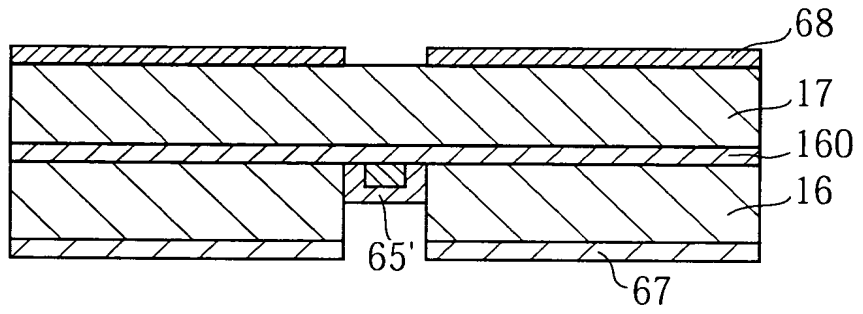


FIG.23C

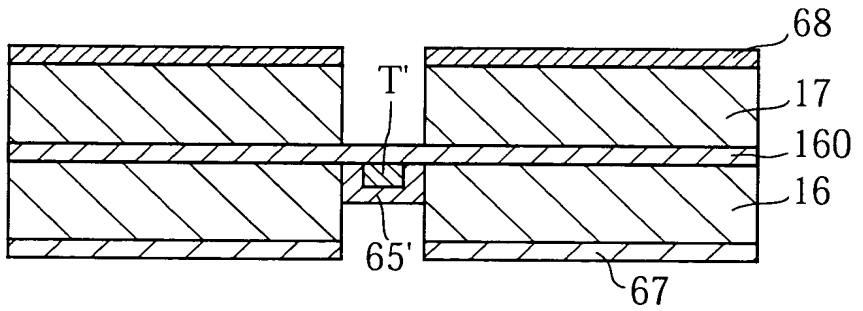
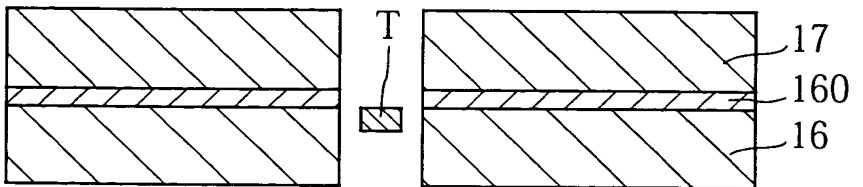


FIG.23D



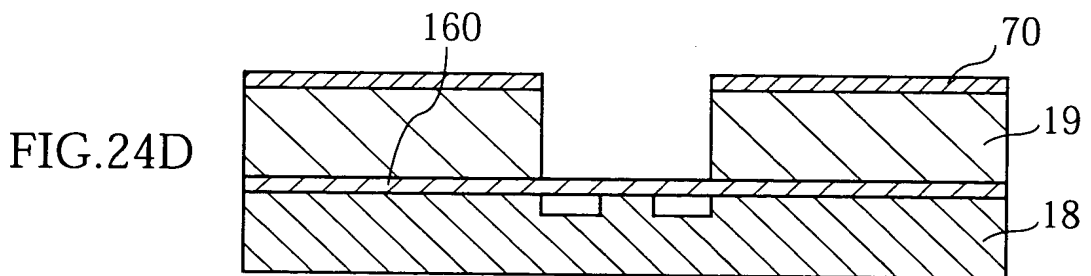
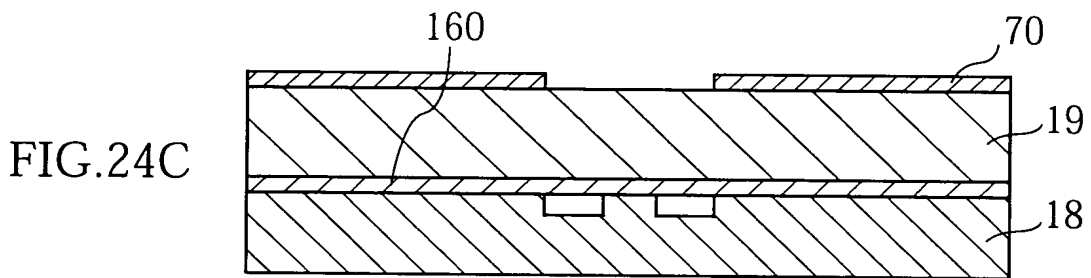
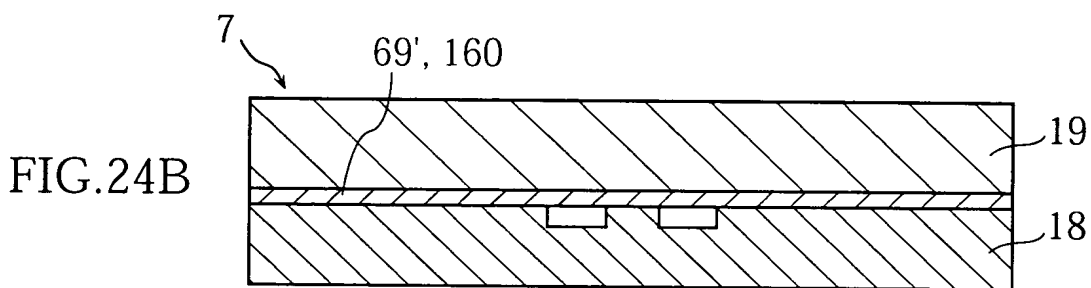
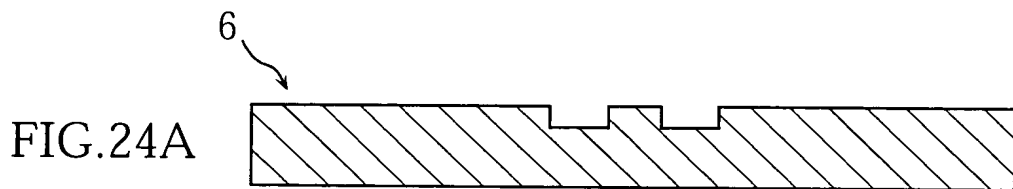




FIG.25A

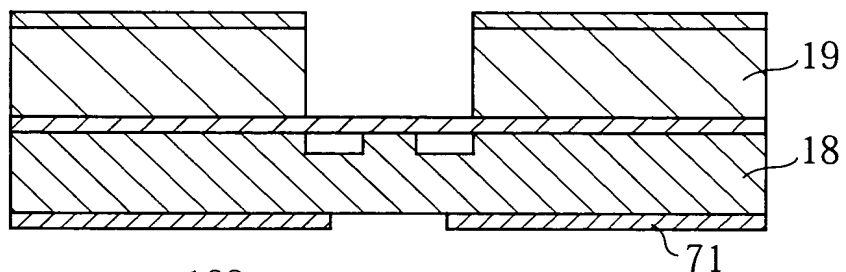


FIG.25B

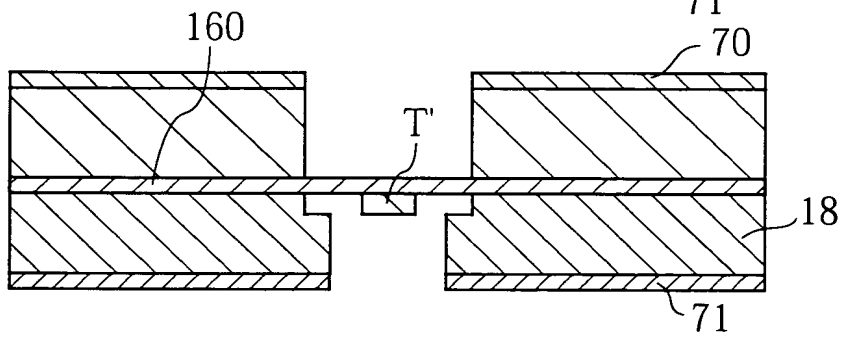
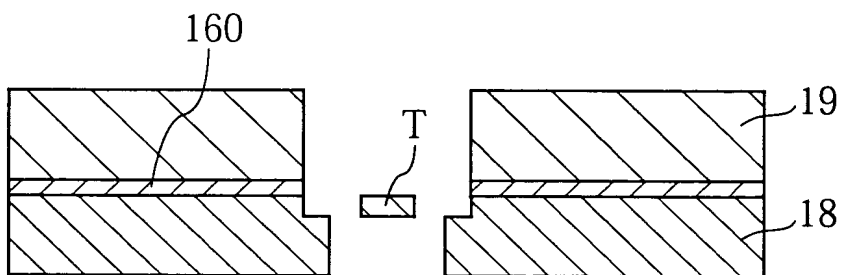


FIG.25C



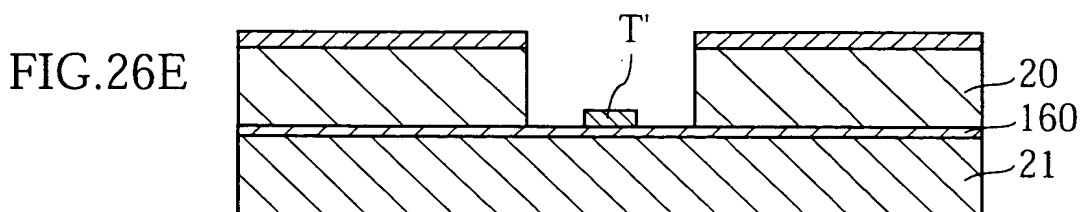
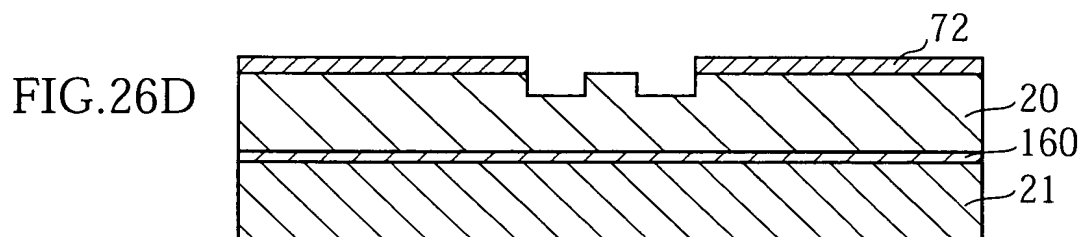
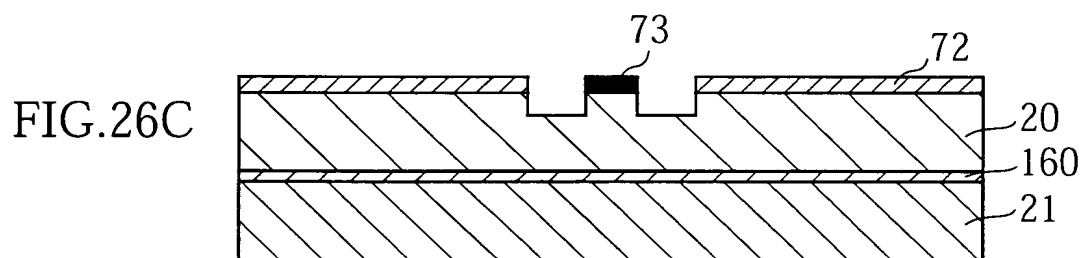
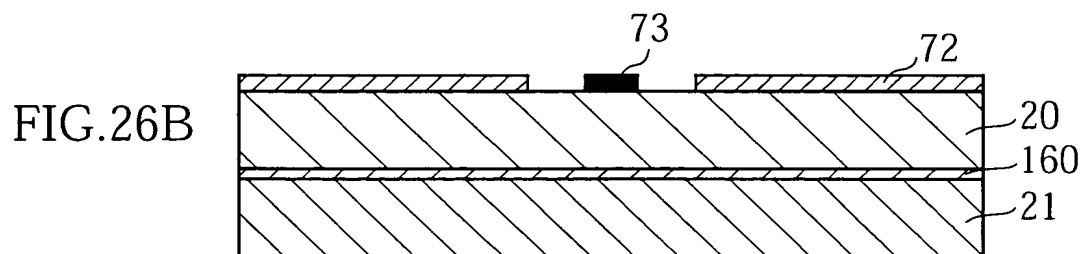
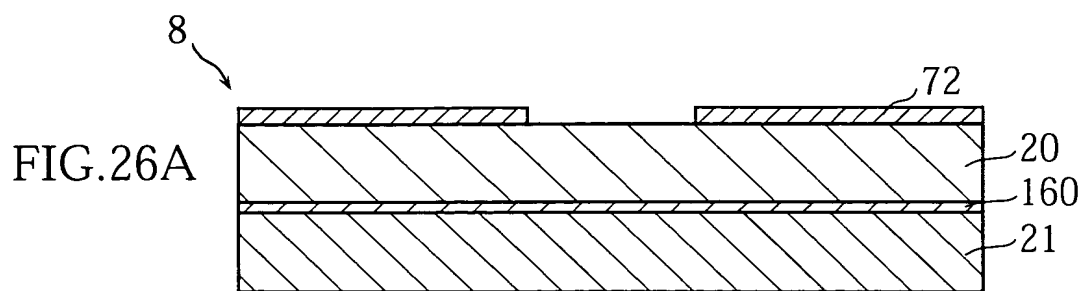


FIG.27A

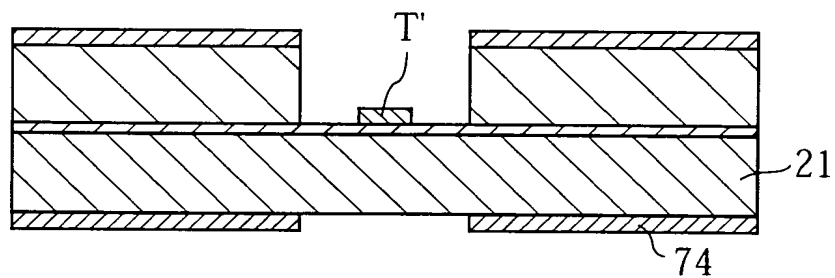


FIG.27B

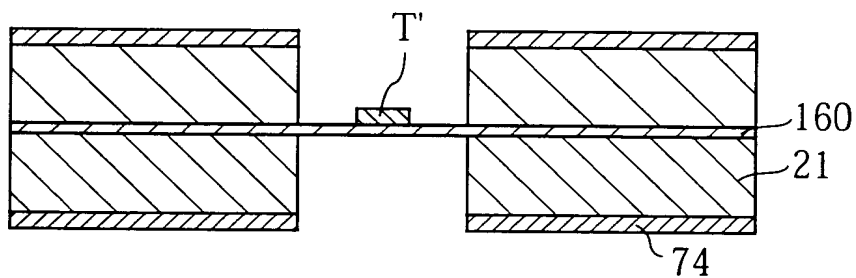
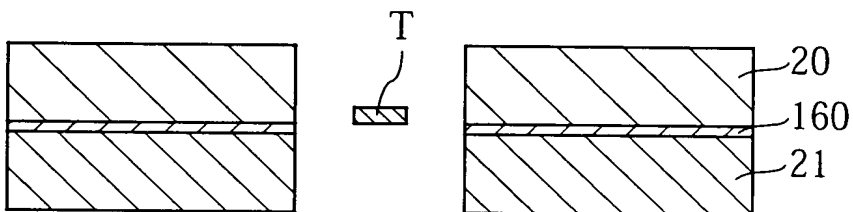
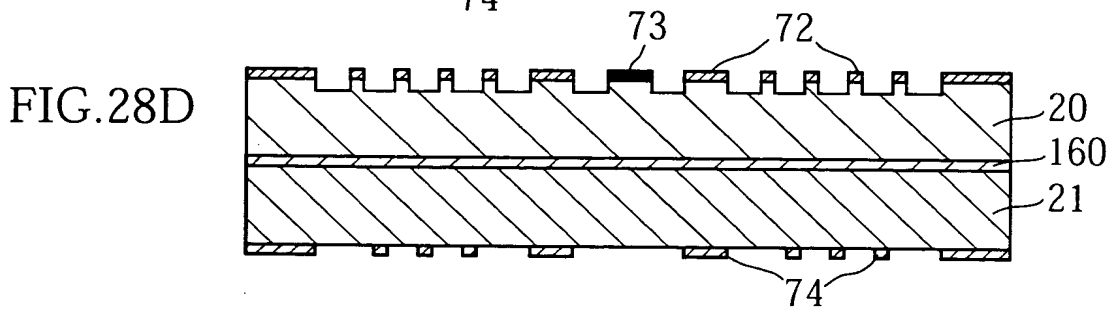
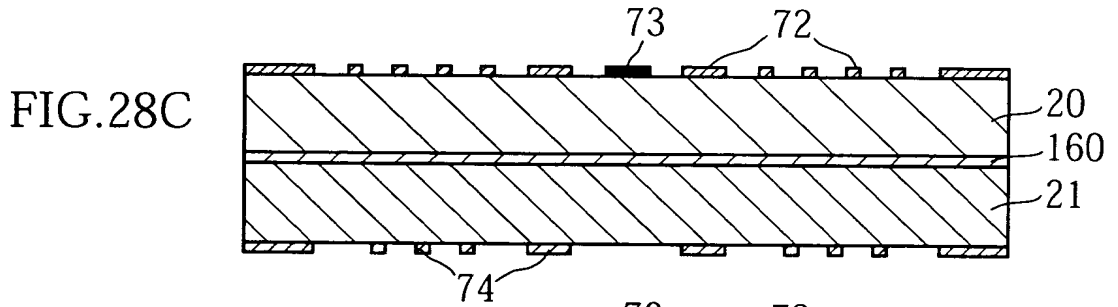
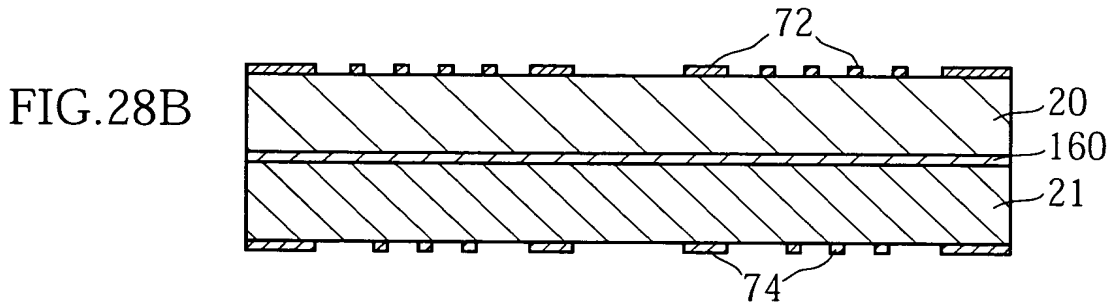
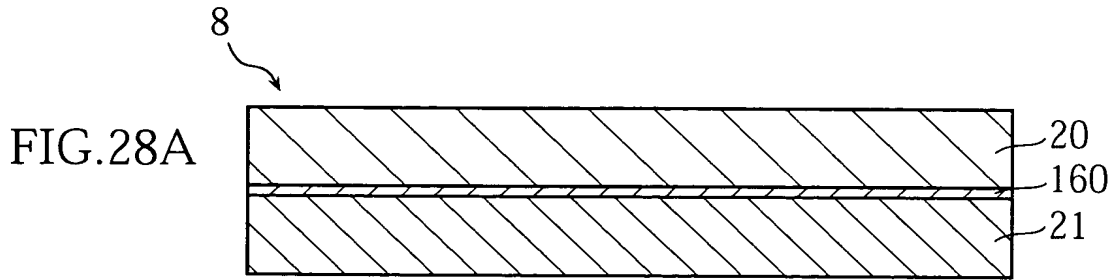
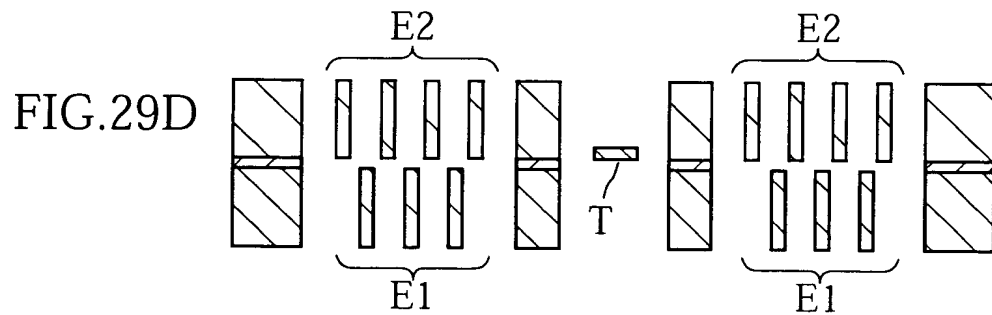
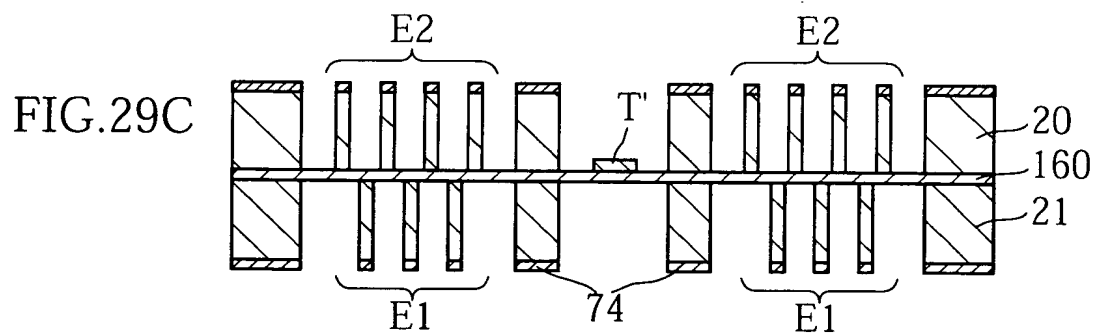
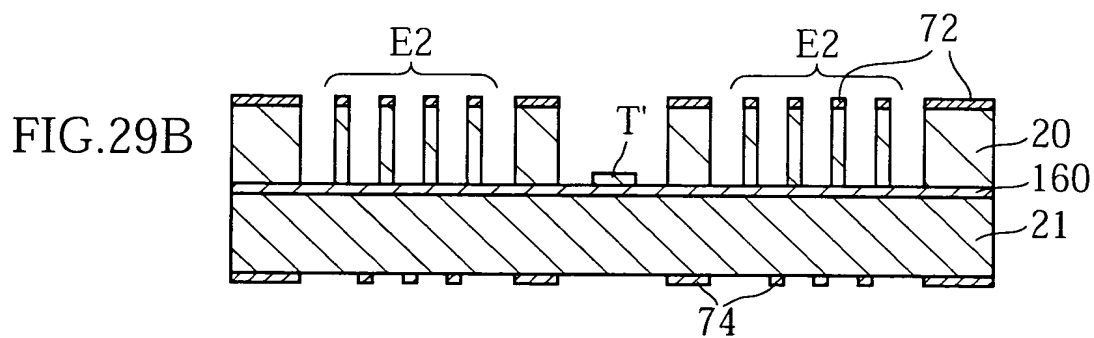
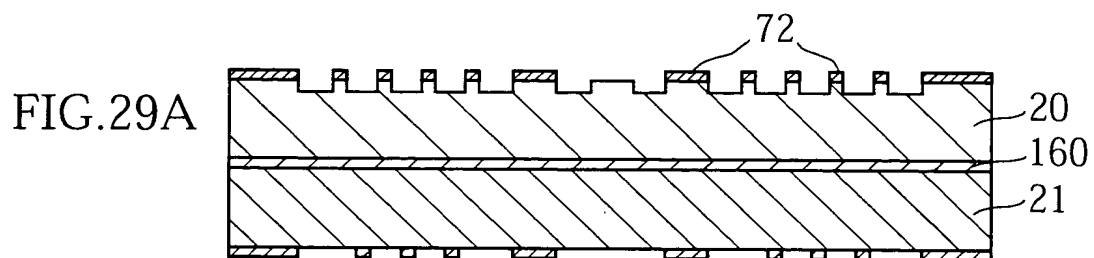
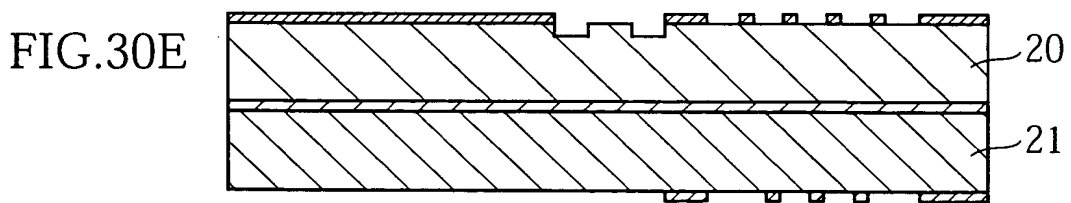
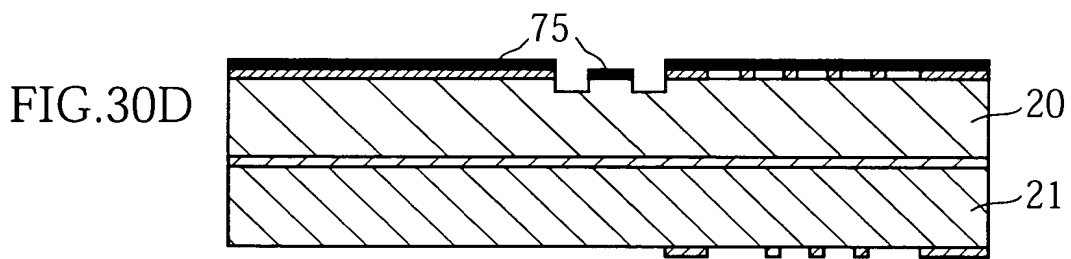
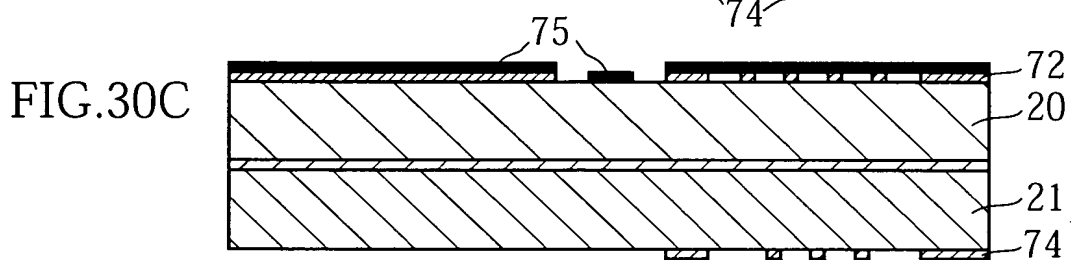
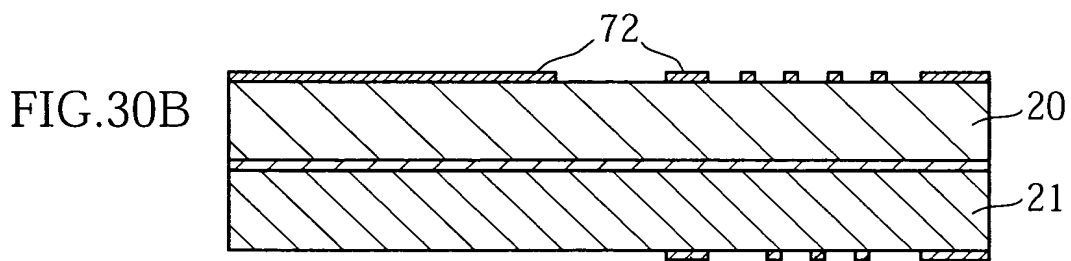
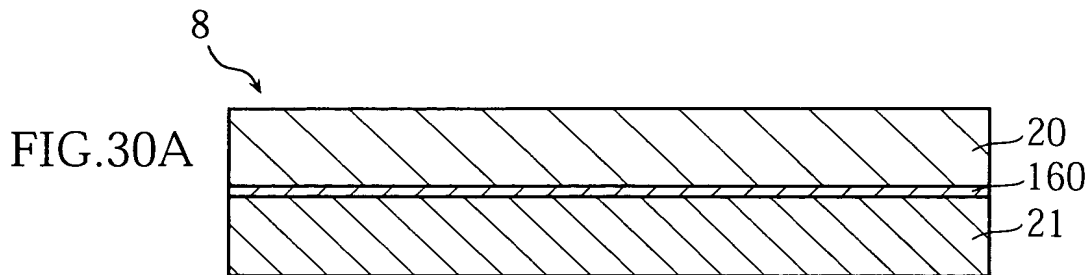


FIG.27C









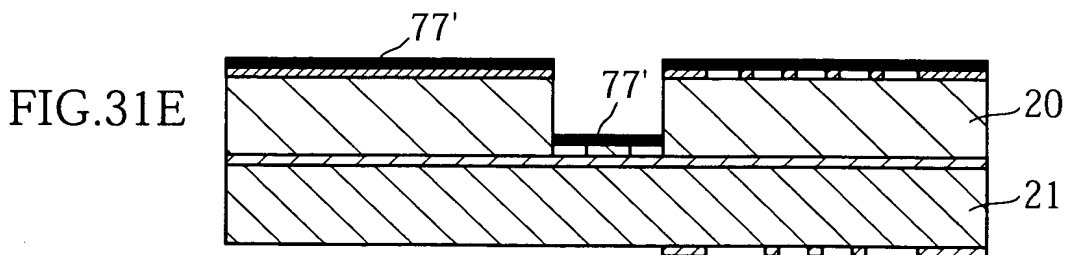
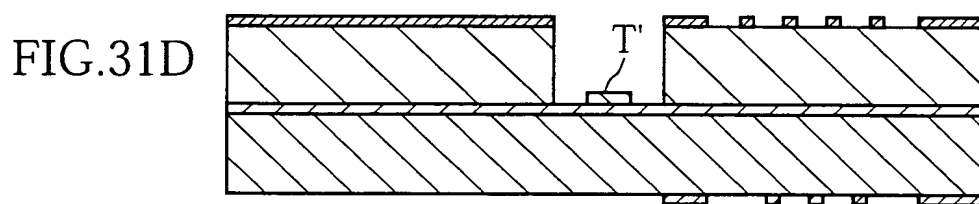
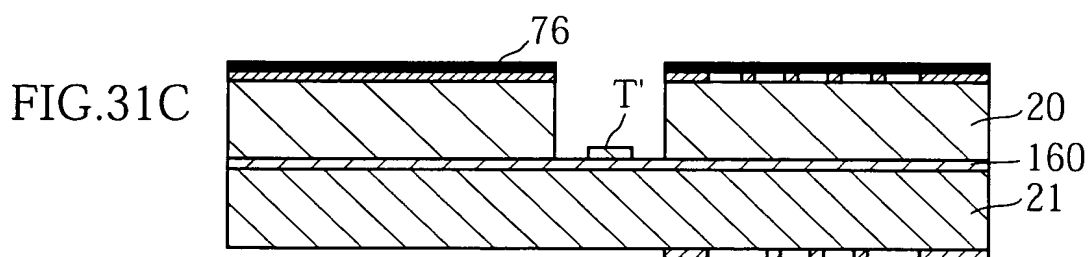
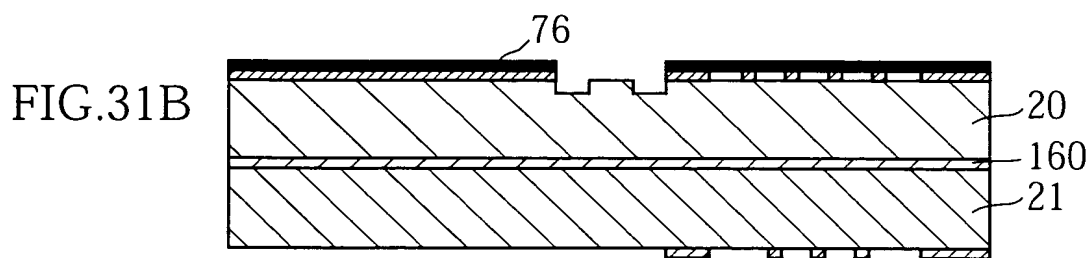
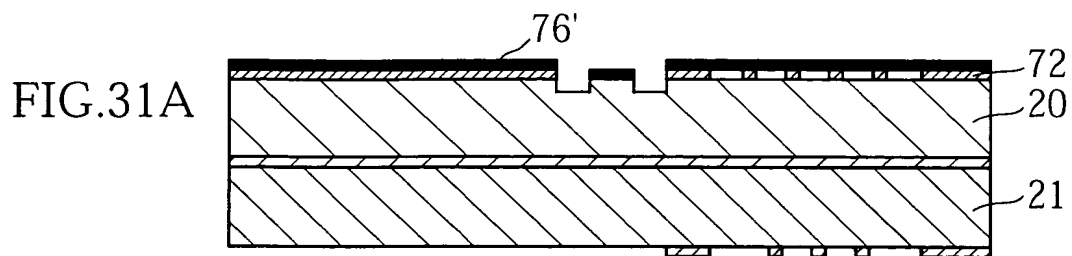


FIG.32A

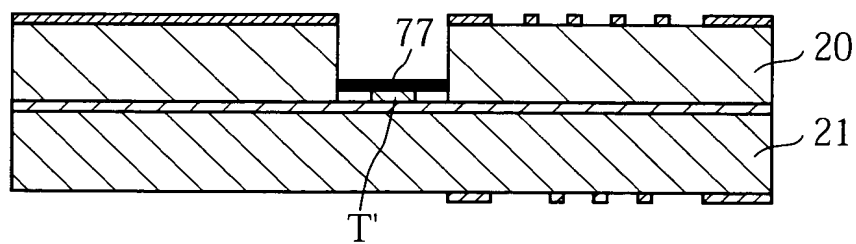


FIG.32B

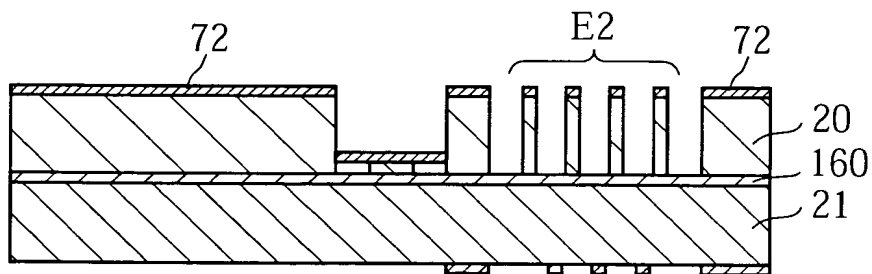


FIG.32C

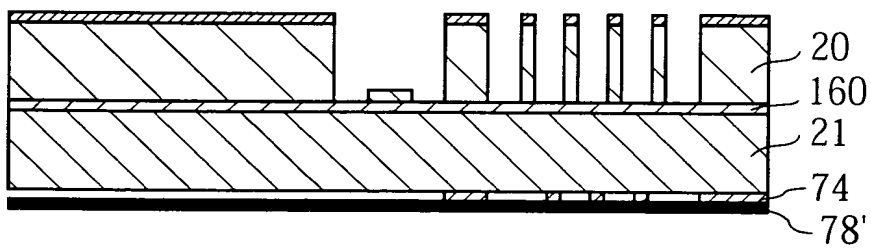


FIG.32D

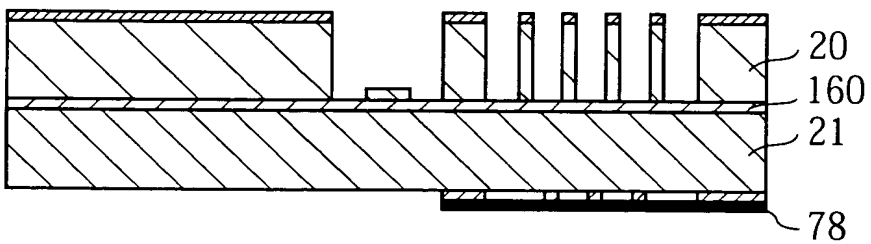
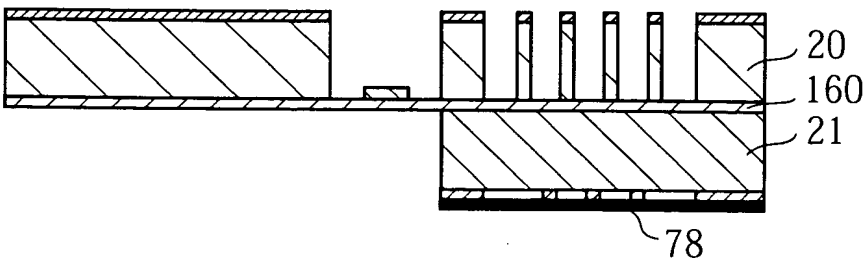
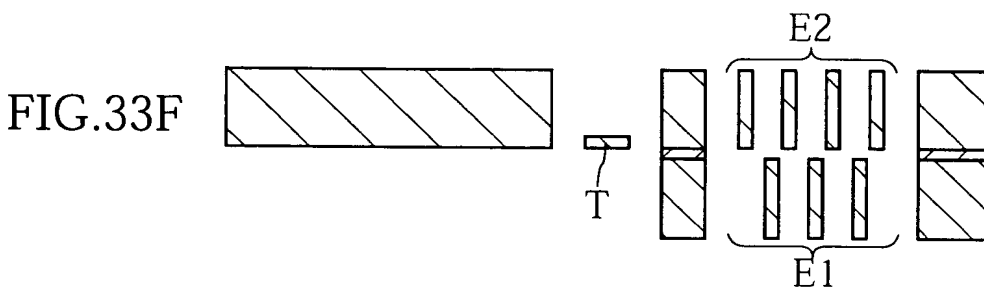
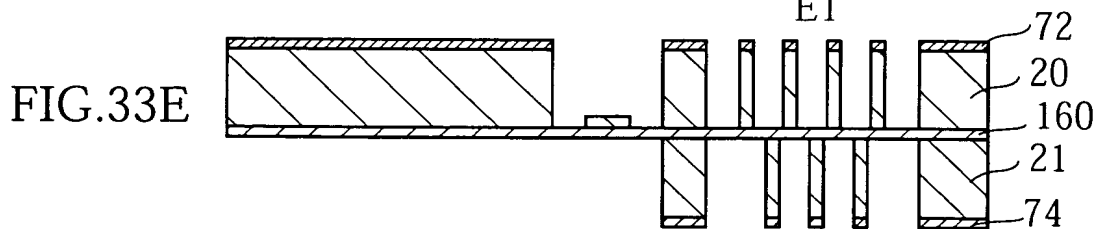
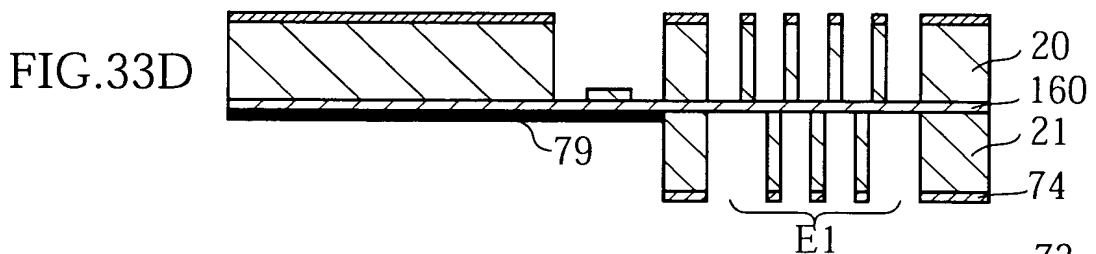
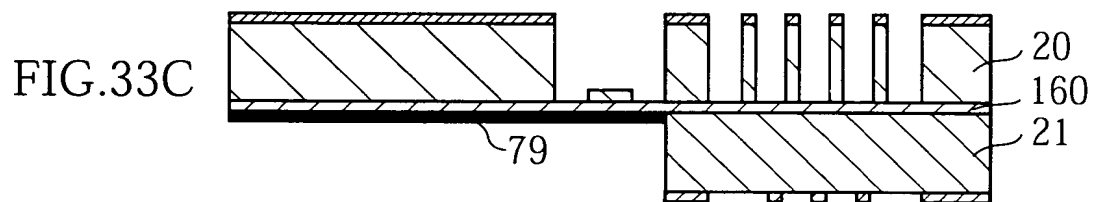
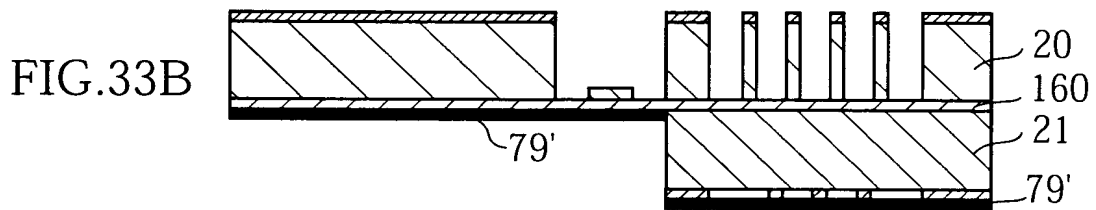
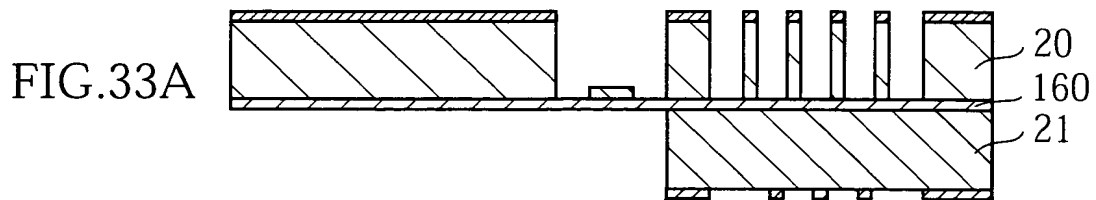


FIG.32E







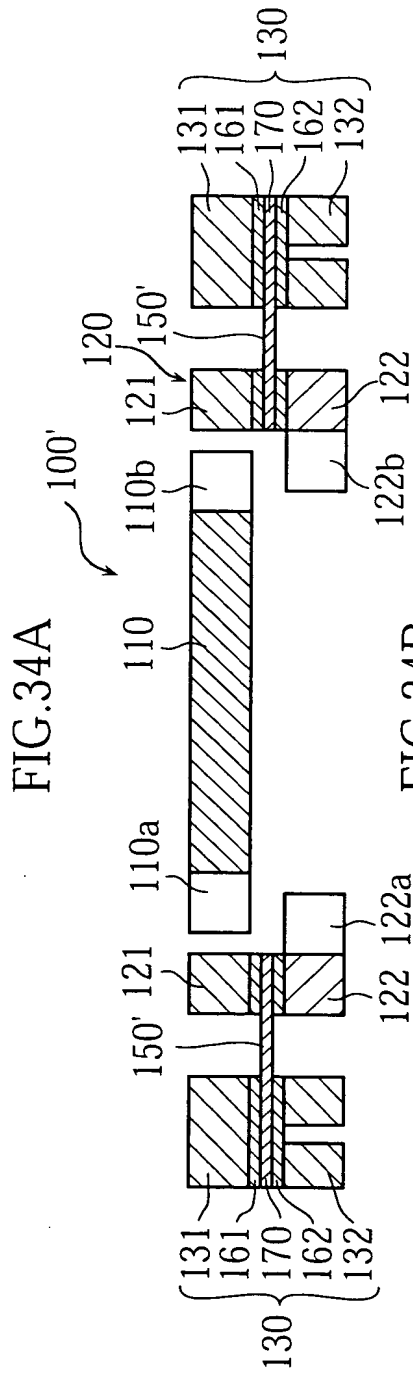


FIG. 34B

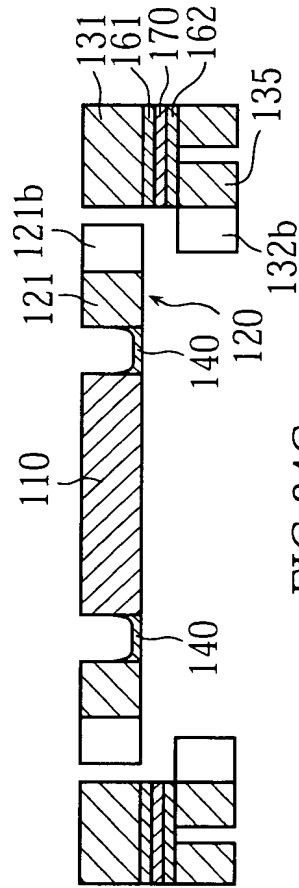
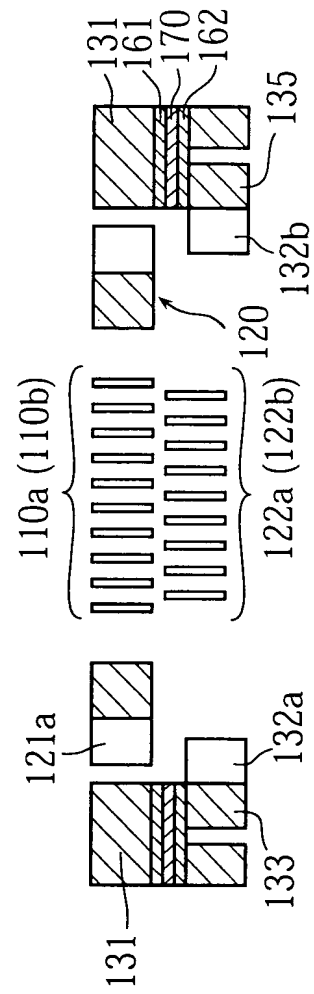
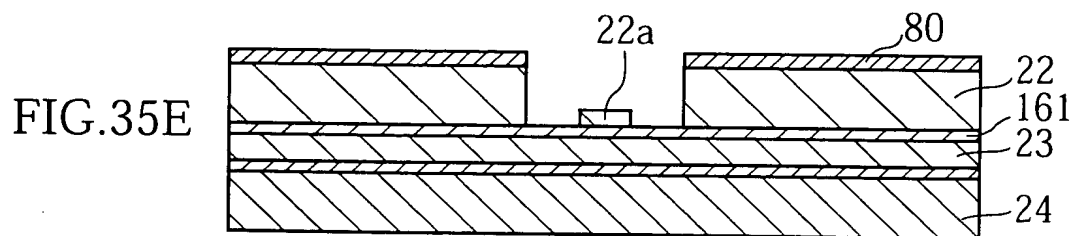
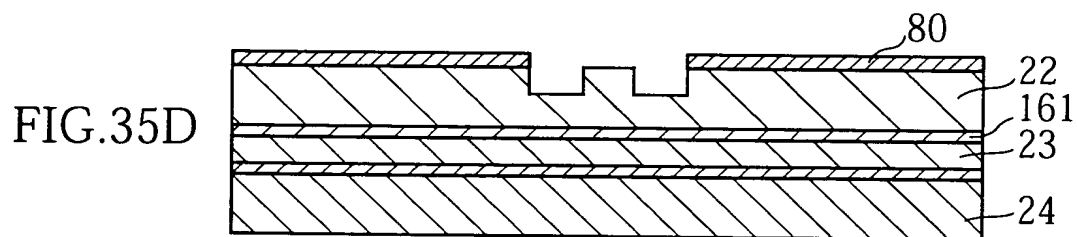
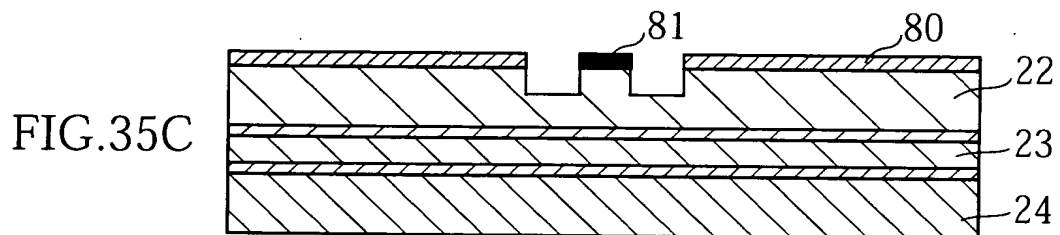
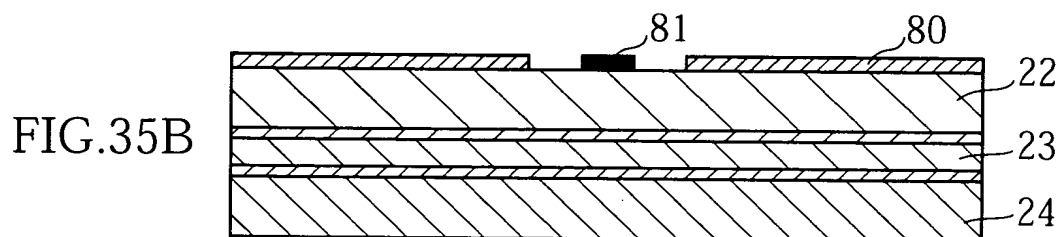
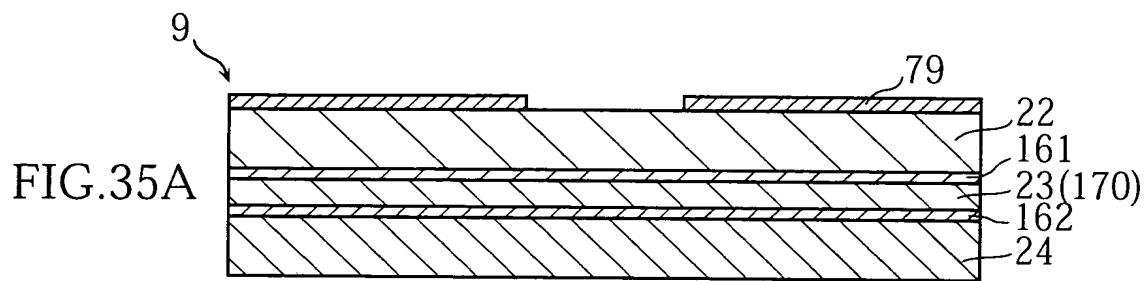
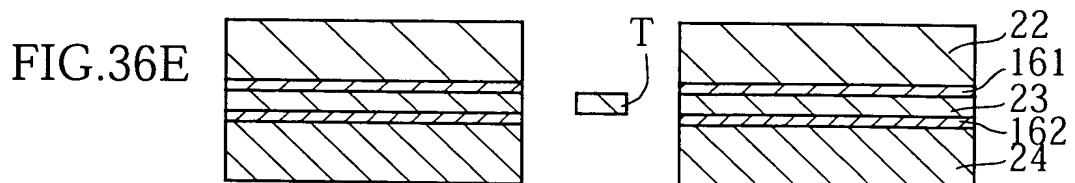
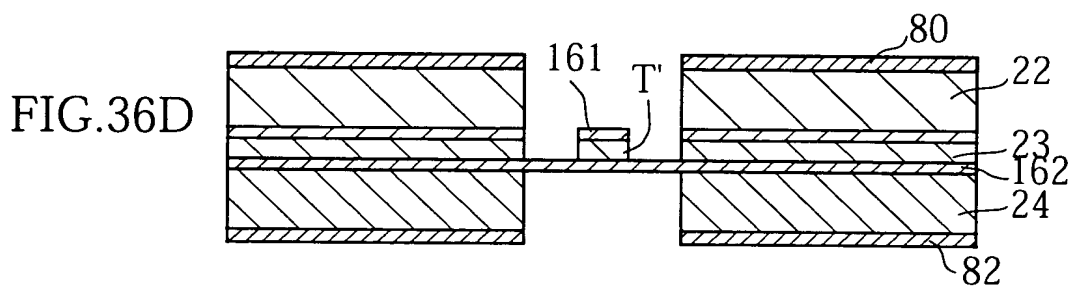
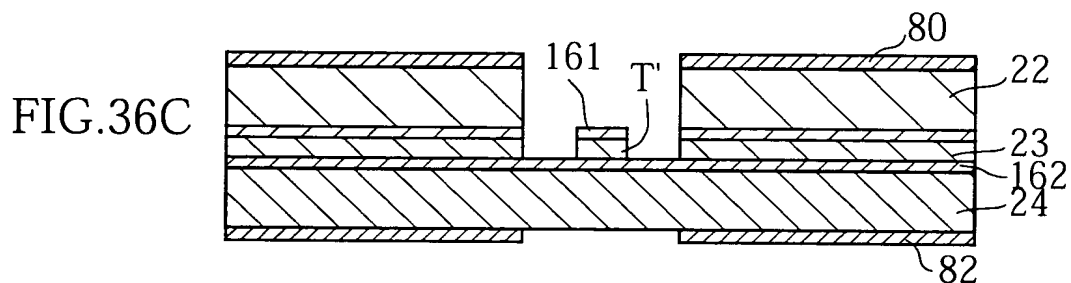
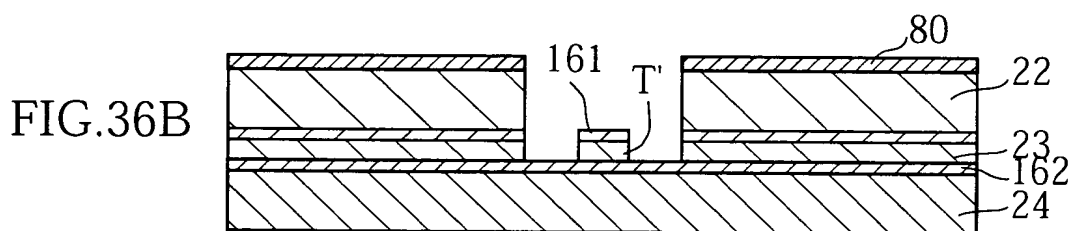
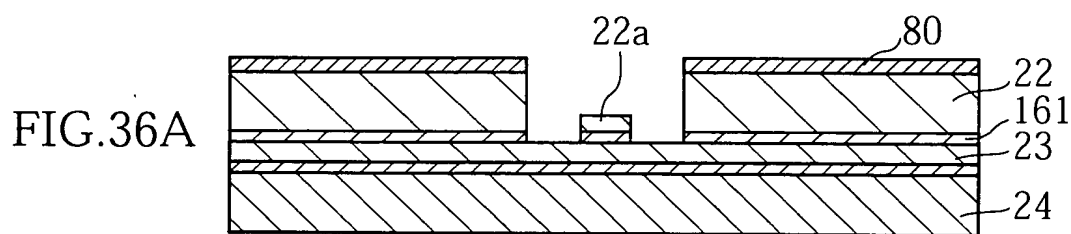


FIG. 34C







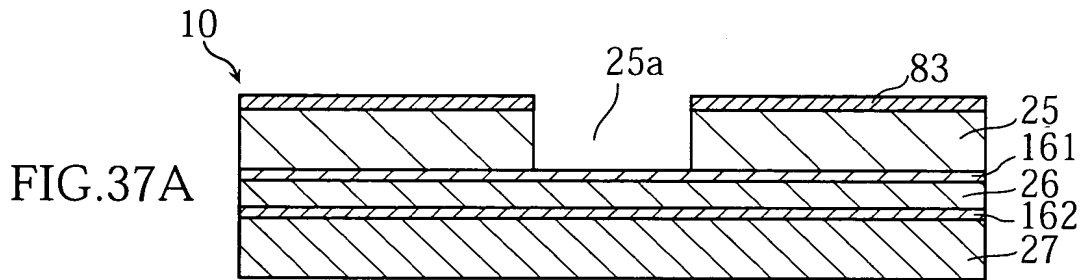


FIG. 37B

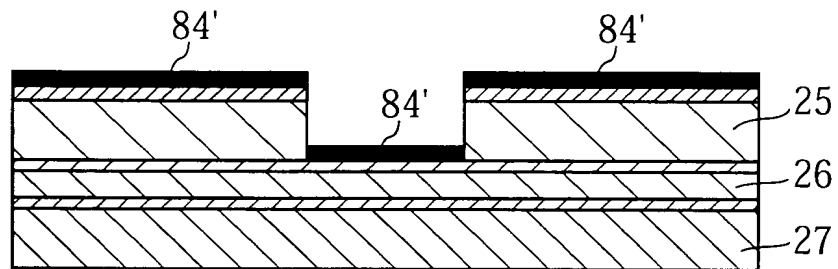


FIG. 37C

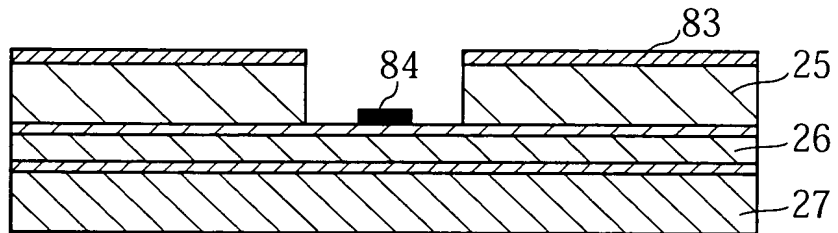
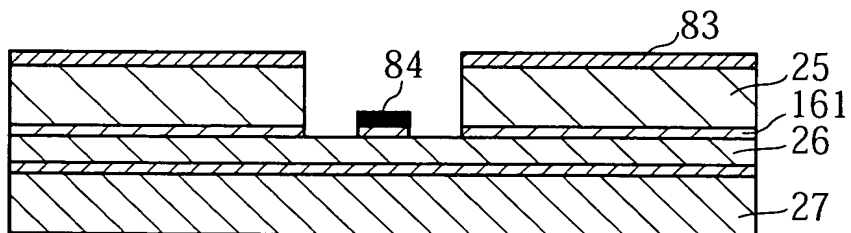


FIG. 37D



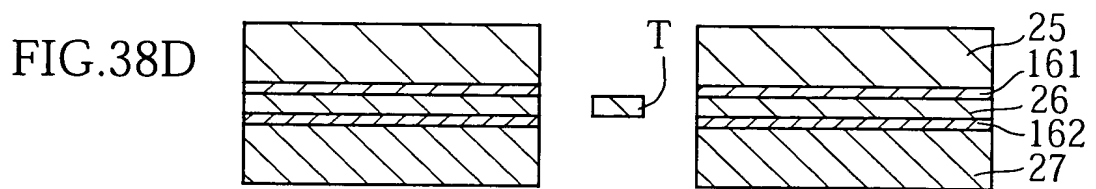
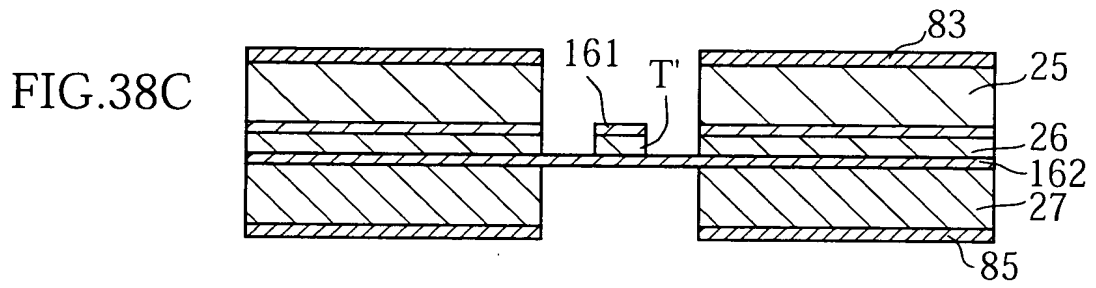
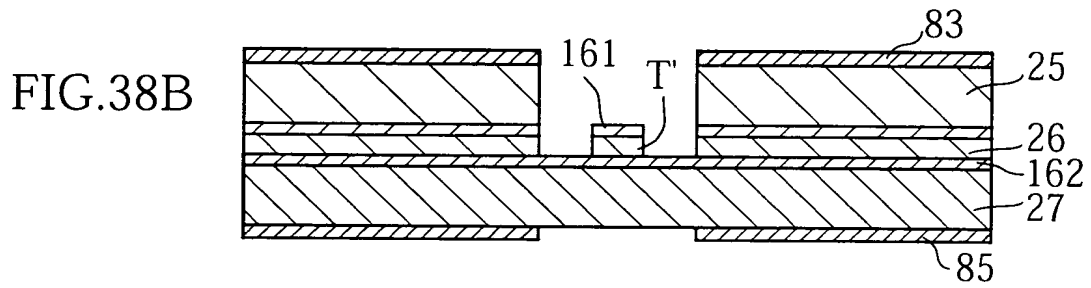
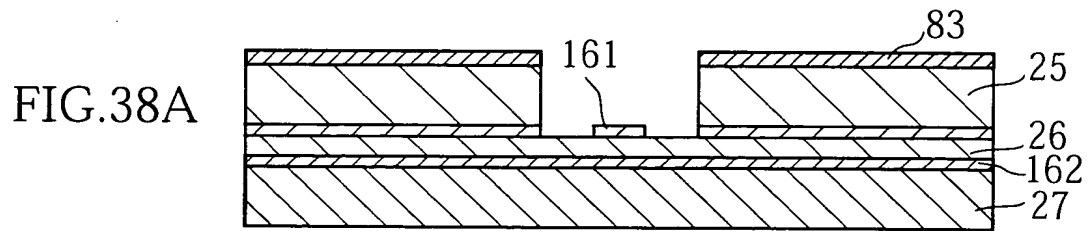


FIG. 39  
PRIOR ART

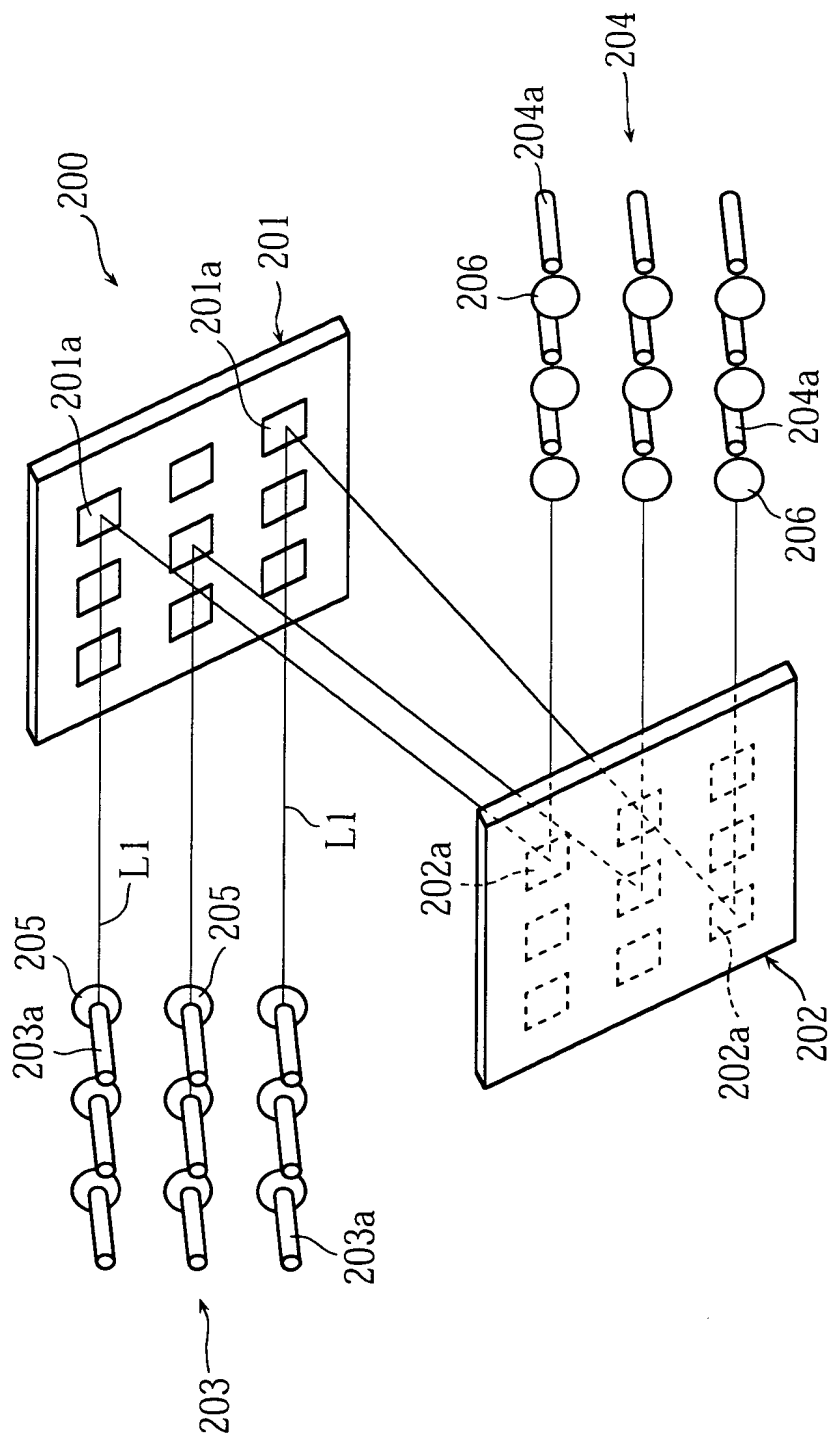


FIG. 40  
PRIOR ART

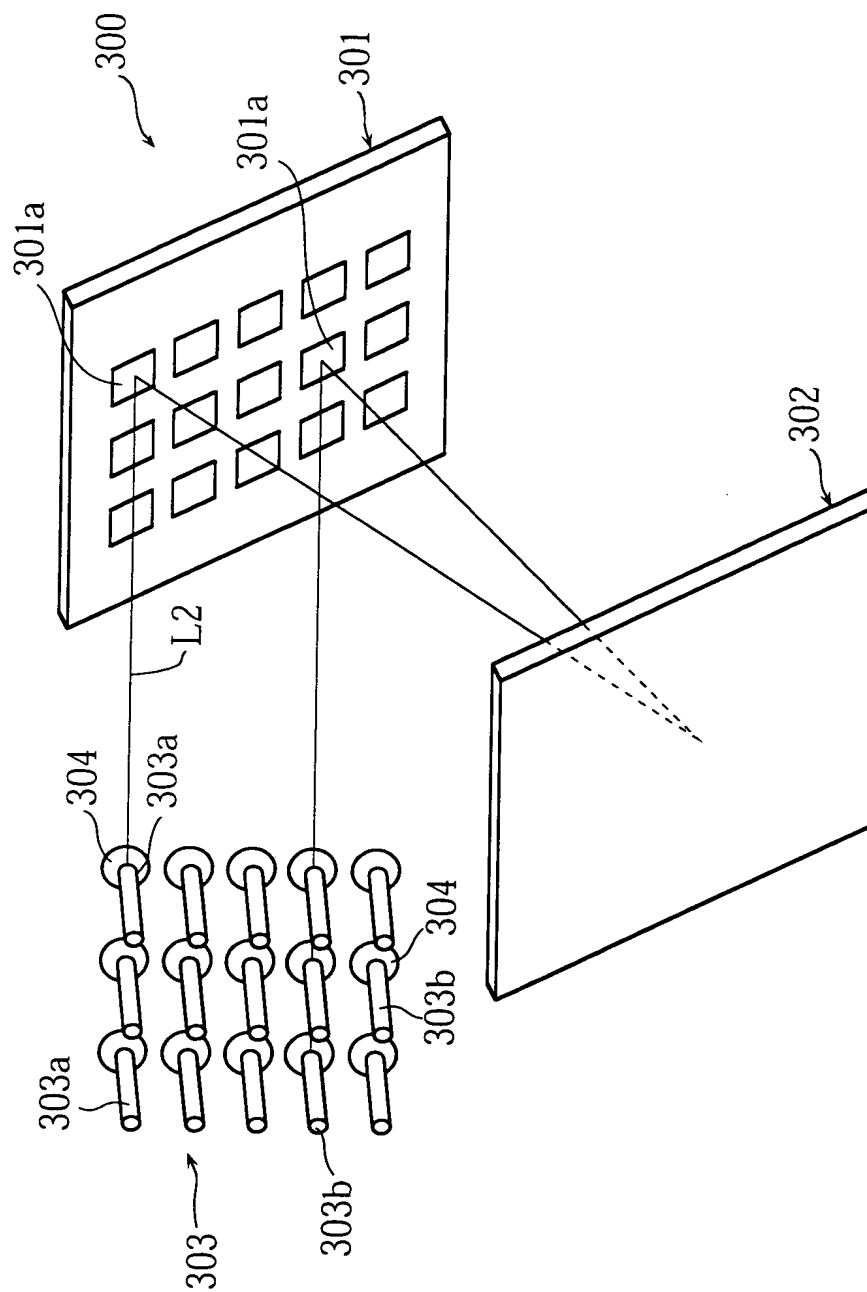








FIG. 43  
PRIOR ART

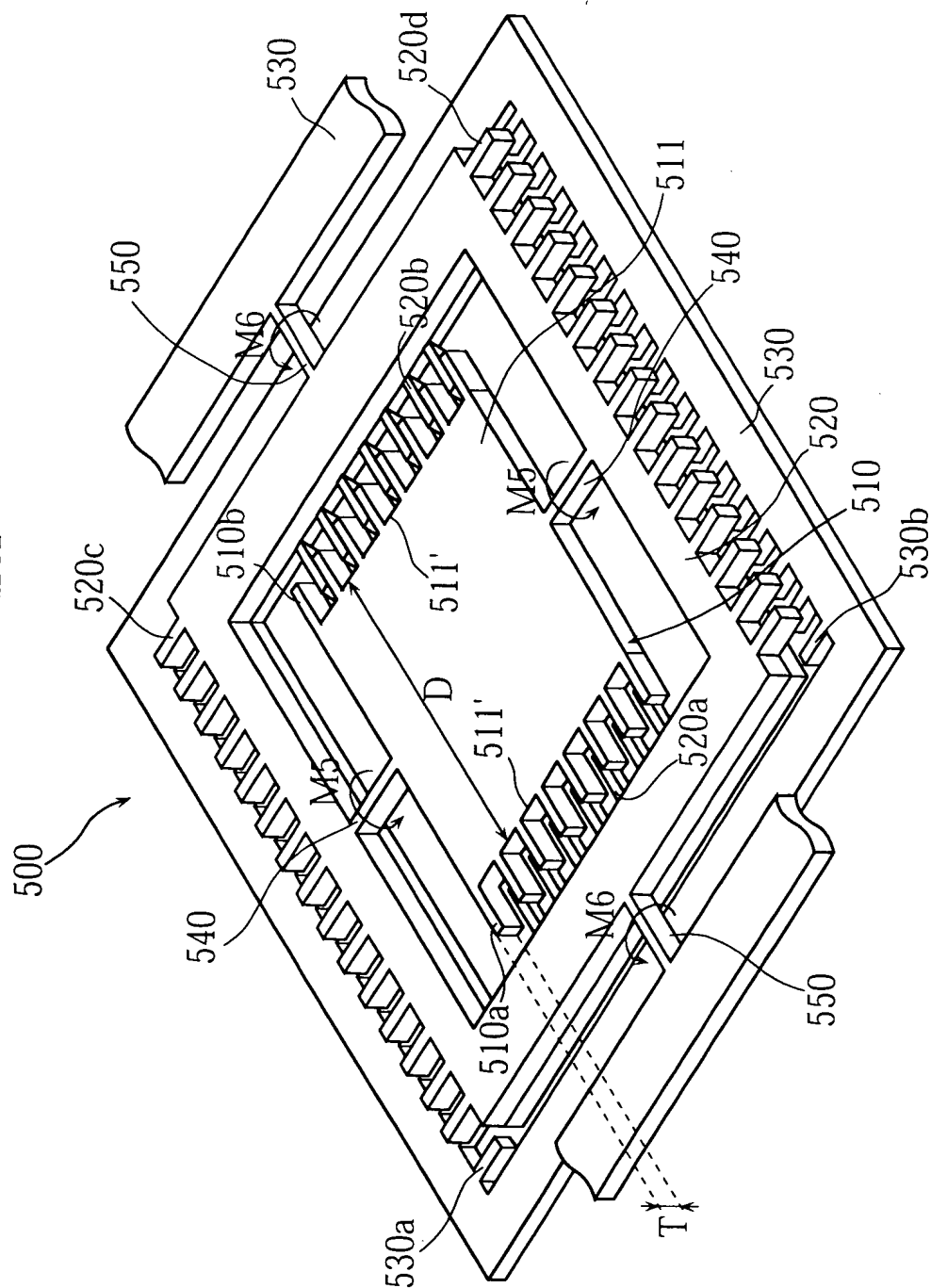


FIG.44A  
PRIOR ART

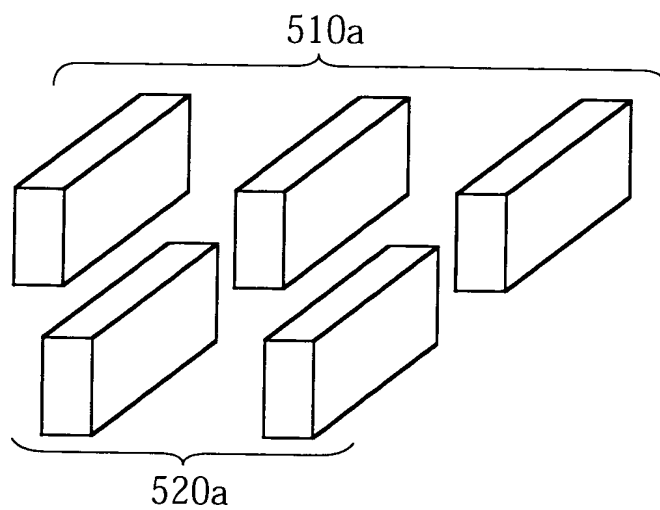


FIG.44B  
PRIOR ART

